

IPR2025-01413
U.S. Patent No. 8,319,512

UNITED STATES PATENT AND TRADEMARK OFFICE

BEFORE THE PATENT TRIAL AND APPEAL BOARD

BOE TECHNOLOGY GROUP CO., LTD.,
Petitioner,

v.

138 EAST LCD ADVANCEMENTS LIMITED,
Patent Owner.

Case No. IPR2025-01413
U.S. Patent No. 8,319,512

DECLARATION OF E. FRED SCHUBERT, PH.D.

I, E. Fred Schubert, of Troy, New York, declare that:

I. ASSIGNMENT

1. I have been retained by Robins Kaplan LLP on behalf of 138 East LCD Advancements Ltd. (“138 East”) as an expert with regard to this matter. I understand that Petitioner BOE Technology Group Co., Ltd. (“BOE” or “Petitioner”) is requesting that the Patent Trial and Appeal Board (“Board”) institute *inter partes* review (IPR) of U.S. Pat. No. 8,319,512 (“the ’512 patent”) (Ex. 1001).

2. In my capacity as an expert, I have been asked to provide my independent analysis and opinions regarding the ’512 patent, the prosecution history of the ’512 patent and related applications as applicable, the alleged prior art relied upon by Petitioner, the meaning of various claim terms from the ’512 patent from the perspective of a person of ordinary skill in the art (“POSITA”), and the opinions offered by Petitioner’s expert, Dr. Manos Tentzeris, in his declaration (“Tentzeris Declaration”) (Ex. 1002). My opinions and conclusions are fully discussed in later sections of this declaration.

3. I am an independent consultant, and I am not, and have never been, an employee of 138 East or BOE. I received no compensation for this declaration beyond my normal hourly compensation (\$600) based on my time spent analyzing the ’512 patent, the prosecution history of the ’512 patent and related applications,

the prior art publications relied upon by Petitioner, the Tentzeris Declaration, and other related materials. I will not receive any added compensation based on the outcome of any IPR or other proceedings involving the '512 patent.

4. This declaration and my opinions are in support of Patent Owner's Preliminary Response, and I understand that the content of this declaration may be expressed and reproduced in the POPR.

II. BACKGROUND AND QUALIFICATIONS

5. I am currently an active, tenured, full professor in the Department for Electrical, Computer, and Systems Engineering at the Rensselaer Polytechnic Institute (RPI) located in Troy, New York.

6. I also held other positions at RPI. For example, from 2002 to 2012, I was a professor in the Department of Physics, Applied Physics, and Astronomy. In 2008-2009, I served as the founding director for RPI's Engineering Research Center for Smart Lighting, which was funded by the U.S. National Science Foundation (NSF).

7. Before I moved to RPI, I was a professor in the Department of Electrical and Computer Engineering at Boston University, from 1995 to 2002. I also served as the director of Boston University's Semiconductor Devices Research Laboratory.

8. Prior to my university career, I was a post-doctoral member of the technical staff, member of the technical staff, principal investigator, and member of management at AT&T Bell Laboratories in Holmdel and Murray Hill, New Jersey, from 1985 to 1995.

9. I earned my Ph.D. in 1986, Master of Science in 1981, and Bachelor's degree in 1978, all in Electrical Engineering, at the University of Stuttgart, Germany.

10. My Curriculum Vitae ("CV") is attached as Appendix A. As shown by my CV, I have substantial experience in the design and implementation of flat panel display devices, including the design, fabrication, processing, and packaging of the components that are commonly used in liquid crystal displays (LCDs) and light emitting diode (LED) displays.

11. I have published over 300 technical articles, mostly at competitive technical conferences and rigorously refereed technical journals. These articles relate to Liquid Crystal Displays (LCDs), LEDs, semiconductor electronics (e.g., field-effect transistors and bipolar junction transistors), semiconductor lasers, and photo-detectors, that is, the technologies which form the foundations of flat panel displays.

12. As an example of my research activities in the field of LCDs, I refer to a U.S. patent issued in 2012: Jaehee Cho, E. Fred Schubert, and Xing Yan

“Liquid crystal display with refractive index matched electrodes” US Patent No. 8,164,727; filed on April 28, 2010; issued on April 24, 2012. During my tenure in industry (AT&T Bell Laboratories), I was part of a working group on LCDs. I have also performed technical consulting services in the field of LCDs and associated TFTs (thin film transistors). One project concerned the enhancement of the carrier mobility in amorphous silicon TFTs. At my university (RPI), I regularly teach courses on microelectronic devices and displays, including TFTs and LCDs. Light emitting diodes are routinely used as a back lighting source for LCDs, and I have worked on and developed LEDs for backlighting units.

13. I am also the author or editor of several books. For example, I authored the textbook “Light-Emitting Diodes,” (1st, 2nd, 3rd, and 4th editions) initially published by Cambridge University Press, Cambridge, UK, with the later editions published on Google Books. In the LED book, I provide a comprehensive review of the state-of-art technologies for designing, fabricating, processing, and manufacturing LEDs, all of which are relevant to LCDs, specifically the associated back-lighting units.

14. In addition to my research, I have been teaching for more than 25 years. I have taught numerous undergraduate and advanced graduate courses in integrated optoelectronics, microelectronics technology, solid-state devices, semiconductor devices, display devices, and light-emitting diodes, all pertinent to

the subject matter in the present case. I have also advised close to 50 Ph.D. and M.S. students while at the RPI and Boston University, in areas such as LEDs, semiconductor electronics, semiconductor lasers, and solar cells.

15. I am the co-inventor of more than 35 issued U.S. patents and associated foreign patents. I was identified as one of the top 1% inventors in the field of optoelectronics, in a 2011 study conducted by Professor Erica Fuchs of Carnegie Mellon University under the support of NSF. Examples of my issued U.S. patents include:

- U.S. Patent No. 7,560,746; issued on July 14, 2009, titled “Light emitting diodes and display apparatuses using the same.”
- U.S. Patent No. 8,164,727, issued on April 24, 2012, titled “Liquid crystal display with refractive index matched electrodes.”

16. I have been actively involved in multiple technical societies, including the American Physical Society (APS), Institute of Electrical and Electronics Engineers (IEEE), Optical Society of America (OSA), Society for Optical Engineering (SPIE). I have served in the organizing committee of multiple technical conferences, including, for example:

- Program committee member and chair of “Display and Solid-State Lighting Devices” conference for OSA/IEEE Conference on Lasers and Electro\ Optics (CLEO), 2003 – 2005.

- Member of the International Advisory Committee of First International Conference on Display LEDs (ICDL), Seoul, Korea, January 31 – February 2, 2007.
- Sub-Committee Chair of Track 6: Displays, Solid-State Lighting, Photovoltaics, and Energy-Efficient Photonics of Asia Communications and Photonics Conference (ACP), Shanghai, China, November 11 – 14, 2014. ACP is the largest and the most influential conference in Asia and Pacific Rim for communications and photonics technologies.

17. My research has been recognized by multiple organizations, universities, and institutions. The following list includes examples of honors that I have received:

- Elected Fellow of the IEEE in 1999. According to the IEEE definition, “the grade of Fellow is one of unusual professional distinction conferred by the Board of Directors only upon a person of extraordinary qualifications and experience.”
- Elected Fellow of the SPIE in 1999. According to the Society’s bylaws, a Fellow “shall be distinguished through his achievements and shall have made outstanding contributions in the field of optics, or optoelectronics, or in a related scientific, technical, or engineering field.”

Elected Fellow of the OSA in 2001. OSA Fellows are elected by the OSA Board of Directors.

- Elected Fellow of the APS in 2001.
- Honored with RPI Medal as Senior Constellation Chair in 2002.
- Recipient of “Scientific American 50 Award” of 2007, as published in the January 2008 issue of Scientific American.
- Received “Rensselaer Polytechnic Institute Trustee Faculty Achievement Award” in 2002, 2008, and 2012.

18. My qualifications and accomplishments are further detailed in my CV, submitted as Appendix A.

III. LEVEL OF SKILL IN THE ART AND BASIS FOR OPINIONS

19. Dr. Tentzeris contends that a POSITA in the field of the '512 patent would have “at least a Bachelor of Science degree in electrical engineering, mechanical engineering, or a related subject, and two or more years of experience working in the field of semiconductor substrates and related circuitry. Such experience would typically include familiarity with the design and fabrication of flexible substrates, integration of integrated circuits onto such substrates, and implementation of on-substrate structures such as inspection electrodes, switching circuitry, and amplification stages for signal monitoring and testing. Additional

education may substitute for professional experience, and significant work experience may substitute for formal education..” Ex. 1002 ¶ 26.

20. I disagree with Dr. Tentzeris’s opinion at least insofar as he opines that a POSITA would have two or more years experience working in the field of “semiconductor substrates.” Semiconductor substrates, such as Si substrates, Ge substrates, or GaAs substrates, are unrelated to the subject matter of the ’512 patent which employs insulating flexible substrates that are typically made of organic polymers.

21. For purposes of this Declaration, however, I do not dispute the level of skill for a POSITA as set forth by Dr. Tentzeris and adopted by Petitioner.

22. Based on my education and experience, which exceed the education and experience of a POSITA as Dr. Tentzeris has proposed, I am qualified to render opinions regarding the technology claimed and described in the ’512 patent. Based on my expertise and qualifications, I am qualified to provide an opinion as to what a POSITA would have understood, known, or concluded as of approximately March 23, 2009, which I understand to be the priority date of the ’512 patent.

23. In reaching my opinions and conclusions, I have relied upon my education, my work experience in the relevant field, and my training, and considered and relied upon my review and analysis of the Petition and its exhibits.

IV. RELEVANT LEGAL PRINCIPLES

24. For the purposes of this declaration, I have been informed about certain aspects of the law that are relevant to my analysis and opinions. I have applied these legal principles in rendering my opinions below.

A. Claim Construction

25. I understand that the ordinary and customary meaning of a claim term is the meaning that the term would have to a POSITA at the time of the invention.

26. In the absence of an express intent on the part of the inventor to give a special meaning to the claim terms, the words are presumed to take on the ordinary and customary meanings in light of the relevant patent attributed to them by a POSITA.

27. I understand that it is the use of the claim term in the context of the written description, and as customarily used by those skilled in the relevant art, that accurately reflects both the ordinary and the customary meaning of the terms in the claims.

28. I understand that the basis for a claim term's ordinary and customary meaning may be derived from a variety of sources, including the words of the claims themselves, the remainder of the specification, the prosecution history, extrinsic evidence concerning relevant scientific principles, the meaning of technical terms, and the state of the art at the time of the invention.

29. I have been instructed that dictionary definitions or definitions from technical references can be used to inform or confirm the ordinary and customary meaning of words found in a claim, but that in construing claim terms, the general meanings gleaned from reference sources, such as dictionaries, must always be compared against the use of the terms in the context of the claim itself.

30. I understand that a patent applicant is entitled to be his or her own lexicographer (in other words, provide his or her own meaning to a word or phrase) and may rebut the presumption that claim terms are to be given their plain and ordinary meaning. To do so, the applicant must clearly set forth a definition of the term that is different from its ordinary and customary meaning. Where the applicant provides an explicit definition for a term, that definition will control interpretation of the term as it is used in the claim in which it appears. I understand that the specification can also be relied on for more than just explicit lexicography to determine the meaning of a claim term. For example, I understand that the meaning of a particular claim term may also be determined by implication, that is, according to the usage of the term in the context of the specification.

B. Obviousness

31. I understand that under U.S. patent law, 35 U.S.C. § 103, a claim is invalid as obvious if the differences sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the

invention was made to a person having ordinary skill in the art to which said subject matter pertains.

32. I am informed that an obviousness analysis requires an assessment of the scope and content of the prior art, the differences between the art and the claims at issue, and the level of ordinary skill in the art. I am told that it is against this backdrop that obviousness is assessed.

33. I am informed that a POSITA is a hypothetical person who is presumed to be aware of all the pertinent prior art. I am also informed that an obviousness analysis may take account of the inferences and creative steps that a POSITA would employ.

V. THE '512 PATENT

A. Overview of the '512 Patent

34. I have reviewed the '512 patent and I provide a summary below. The '512 patent (U.S. Patent No. 8,319,512), titled "Flexible Substrate Including Inspection Electrode for Outputting Signal Processed in Integrated Circuit, Electro-Optical Device, and Electronic Device," is directed to improved flexible substrates for electro-optical devices such as LCD panels. *E.g.*, Ex. 1001 ('512 Pat.), 1:11-15 ("The present invention relates to a flexible substrate that is to be connected to a liquid crystal device."). The patent addresses the problem of how to reliably monitor signals processed by a driver integrated circuit (IC) mounted on the

flexible substrate without increasing the number of terminals on the LCD panel.

Id., 1:26-33 (“The integrated circuit formed on the flexible substrate is inspected, for example, by monitoring a signal processed in the integrated circuit. If a terminal is provided on the liquid crystal panel in order to monitor the signal, the number of terminals that connect the flexible substrate to the liquid crystal panel is increased.”). The ’512 patent further recognizes the problem that inspection electrodes mounted on the LCD panel itself were incapable of analyzing signals used for internal processing in the IC and not provided to the LCD panel. *Id.*, 1:33-36 (“In addition, the terminal provided on the liquid crystal panel cannot monitor a signal (that is not output from the flexible substrate) used only for internal processing of the integrated circuit. That is, the aforementioned technique has a problem that a signal may not be appropriately monitored.”). The ’512 patent claims priority to a Japanese patent application (JP 2009-069825) filed March 23, 2009. *Id.* at 1.

35. To solve these problems, the ’512 patent discloses a flexible substrate including an inspection electrode located on the flexible substrate itself, electrically connected to the IC and capable of outputting signals processed in the IC, including signals that are not output through the terminals on the flexible substrate. *Id.*, 2:26-28, 2:30-37 (“Since the inspection electrode is located on the flexible substrate, it is not necessary that a similar electrode be provided outside the

flexible substrate.”). By placing the inspection electrode on the flexible substrate rather than on the LCD panel, the ’512 patent invention avoids increasing the number of terminals on the LCD panel itself, where space is limited. *Id.*, 2:30-32 (“This configuration is effective when a layout of lines or a pitch of connection terminals is restricted in order to reduce the size of the flexible substrate.”).

Further, by placing the inspection electrode on the flexible substrate, the ’512 patent inventions allow for monitoring signals used only for internal IC processing and not provided to the LCD substrate. *Id.*, 2:32-37, 2:53-59 (“A signal that is not output from the flexible substrate, or a signal used only for the internal processing of the integrated circuit, can be monitored. In other words, a signal that cannot be monitored by a similar inspection terminal provided outside the flexible substrate [can] be monitored.”).

36. The specification further explains that the inspection electrode may be configured with structural features that enhance reliability and manufacturability. For example, the electrode may have a width larger than each of the lines on the substrate, which facilitates more reliable contact with a test probe. *Id.*, 3:40-48. (“inspection electrode has a width larger than the width of each of the lines”).

37. The ’512 patent further discloses and claims circuitry in the IC itself for controlling whether the inspection electrode outputs a processed signal; through this switching operation, the inspection electrode is “capable of outputting a signal

only when the signal needs to be monitored,” which reduces power consumption of the inspection electrode. *Id.*, 2:60-3:5.

38. The ’512 patent also discloses and claims circuitry in the IC to switch the types of signals output from the IC and provided to the inspection electrode. *Id.*, 3:10-12. Signal types may include a clock signal, a start signal, or a timing signal, for example. *Id.*, 8:44-46. The ’512 patent explains that by switching the types of signals output from the IC to the inspection electrode, “signals of different types can be output from the inspection electrode even when the number of inspection electrodes provided on the flexible substrate is only one.” *Id.*, 3:15-18. This modification allows many signals to be inspected independent of the number of inspection electrodes, therefore saving space on the flexible substrate. *Id.*, 3:18-20.

B. Related District Court Litigation

39. I am aware of related District Court cases involving the same parties, and where the ’512 patent has been asserted and validity of the ’512 patent claims has been challenged.

VI. ANALYSIS OF SAITO IN VIEW OF HER (GROUND 1)

40. To begin, I note that Dr. Tentzeris contends that “all of the elements described in the ’512 patent were well known in the industry well before the March 23, 2009 priority date,” and he offers discussion of background technology, the

purported state of the art, and various references that the Petition does not include as part of the asserted obviousness combinations. *See, e.g.*, Ex. 1002, ¶¶ 34-42. I disagree that the claimed inventions of the '512 patent are obvious or conventional, including for reasons I provide here. I do not separately discuss many of these additional references here, as they are not material to my opinion that neither Dr. Tentzeris nor the Petition shows that any of the challenged claims are rendered obvious by the asserted combinations. I reserve my right to address these aspects of Dr. Tentzeris's declaration and the Petition at a later date, should the Board institute these proceedings.

A. Overview of Saito

41. I have reviewed the Saito reference and summarize certain aspects of its disclosure here. U.S. Patent No. 6,300,997 to Saito et al. is titled "Liquid Crystal Display Device Having an IC Chip Mounted on a Narrow Film Wiring Board." Unlike the '512 patent, which is directed to efficient placement and operation of an inspection electrode on a flexible substrate, Saito is chiefly concerned with reducing the width of a film wiring board used to mount a driver IC while maintaining reliable electrical connection to the LCD panel. *See* Ex. 1004 (Saito), Abstract.

42. In particular, Saito explains that the film wiring board in conventional LCD modules required a width sufficient to accommodate bonding leads that align

with the terminals arranged along the edge of the LCD panel. The width of the wiring board was therefore constrained by the arrangement of the terminals on the LCD panel substrate. This width limitation was therefore a limiting factor in reducing device size and manufacturing cost while causing increased complexity in positioning and bonding to connect the flexible wiring board to the LCD panel. Ex. 1004, 2:8-18.

43. To address this problem with conventional LCD modules, Saito teaches a particular arrangement of the terminals on the LCD panel to achieve a more compact terminal layout region; this arrangement allows the film wiring board to be smaller, reducing manufacturing costs and improving bonding reliability between the flexible wiring board and the LCD panel. In particular, Saito teaches arranging the segment terminals and common terminals in a densely packed configuration where the terminals that connect with the flexible wiring board are grouped centrally and symmetrically, which allows a substantial reduction in the width of the flexible wiring board. *Id.*, Fig. 2A, 6:27-33.

44. Unlike the '512 patent, which is concerned with testing signals output from an IC, Saito is directed to a specific design problem, namely panel terminal geometry and film-board width. Saito does not provide any teaching of amplifying, switching, or selectively outputting internal or external IC-generated signals. Saito discloses using test pads (62, 63, 64, and 66 in Figure 3) only “to inspect whether

the semiconductor chip 53 is satisfactorily connected to lead wires 54, 55, 56, and 57.” *Id.*, 5:43-46. Further, Saito does not provide any teaching or motivation concerning how to provide a dedicated inspection electrode on a flexible substrate or how to monitor signals that are not supplied to the LCD panel or that are not otherwise available at the output terminals of the flexible substrate. Instead, Saito’s test pads are provided on lines 54-57, which include “output lead wires 54 for the segment terminals,” “output lead wires 55 and 56 for the common terminals” and “input lead wires” that are “connected to the semiconductor chip 53.” *Id.*, Fig. 3, 4:17-21, 4:51-54.

B. Overview of Her

45. I have reviewed the Her reference and summarize certain aspects of its disclosure here. U.S. Patent Application No. 2004/0183563, listing inventors Her and Han, is titled “Semiconductor Integrated Circuit Including Test Pins and Method for Testing Thereof.” Her is chiefly concerned with using a single test pin to test semiconductor integrated circuits having a large number of data-output pins. *See* Ex. 1007 (Her), Abstract.

46. Her explains that conventional IC test devices needed numerous test pins to match the IC’s output pins. *Id.*, ¶ [0006]. Her notes that as LCD resolutions increased, the number of data-output pins grew correspondingly, making it

impractical for test devices to provide a sufficiently large number of test pins. *Id.*, ¶ [0007].

47. Her teaches solving this scalability problem by providing a single “test pin” on the IC and operating the IC in a special test mode in which the IC sequentially outputs its various output signals to the one test pin under control of a clock signal. *E.g., id.*, ¶ [0009], Figs. 2, 4. Under normal mode operation, the data-processing circuit outputs signals to the numerous data-output pins. In test mode operation, however, the output circuit routes those signals—one by one—to the test pin. *See id.*, Figs. 2, 4 (illustrating sequential signal output). This test mode procedure allows a test device with only one pin to test an IC having many outputs. *Id.*, ¶ [0037].

48. Unlike the ’512 patent, which is directed to testing selected IC output signals with an inspection electrode on the flexible substrate, Her is concerned with multiplexing of output signals in the IC in a special test mode. While the ’512 patent teaches a test pad on the flexible substrate itself (outside of the IC), Her’s test pin is located in an “inner circuit” of the IC itself. *See id.*, ¶ [0022], Fig. 2 (showing test pin “TP” as component of IC 100). Her does not teach a flexible substrate at all¹ (let alone a test pad on a flexible substrate), and the problem

¹ In discussing the purported motivation to combine Saito and Her, Dr. Tentzeris states that both “are directed to testing signals processed in an integrated circuit

addressed by Her—the difficulty in testing many output pins with conventional test equipment—differs from the '512 patent's focus on providing reliable, non-intrusive access to IC-processed signals from the flexible substrate on which the IC is mounted.

C. The teachings of Saito in view of Her do not satisfy all elements of any of claims 1-4, 6, or 8-9² of the '512 patent.

1. *Claim 1[f]: “a switching section that switches an operation of the inspection electrode on/off to cause the inspection electrode to output or not to output the signal processed in the integrated circuit”*

49. In my opinion, Saito in view of Her does not disclose or render obvious “a switching section that switches an operation of the inspection electrode on/off to cause the inspection electrode to output or not to output the signal processed in the integrated circuit.” Ex. 1001, claim 1[f].

50. To start, I understand that the Petition and Dr. Tentzeris concede that the asserted lead reference, Saito, does not disclose the “switching section” recited in claim 1[f]. Ex. 1002, ¶ 94; Pet., 32. I agree—Saito does not describe any

formed on a flexible substrate used to drive the display panel.” Ex. 1002, ¶ 67. I disagree with Dr. Tentzeris. Her does not provide any disclosure of a flexible substrate, and I note that Dr. Tentzeris does not cite to any specific disclosure in Her to support his (in my opinion, incorrect) statement.

² I have been informed that Patent Owner has disclaimed claims 10, 11, and 12 of the '512 patent with the United States Patent Office. Therefore I do not address those claims in this declaration, even where they were otherwise included in Petitioner's Grounds and/or addressed by Dr. Tentzeris.

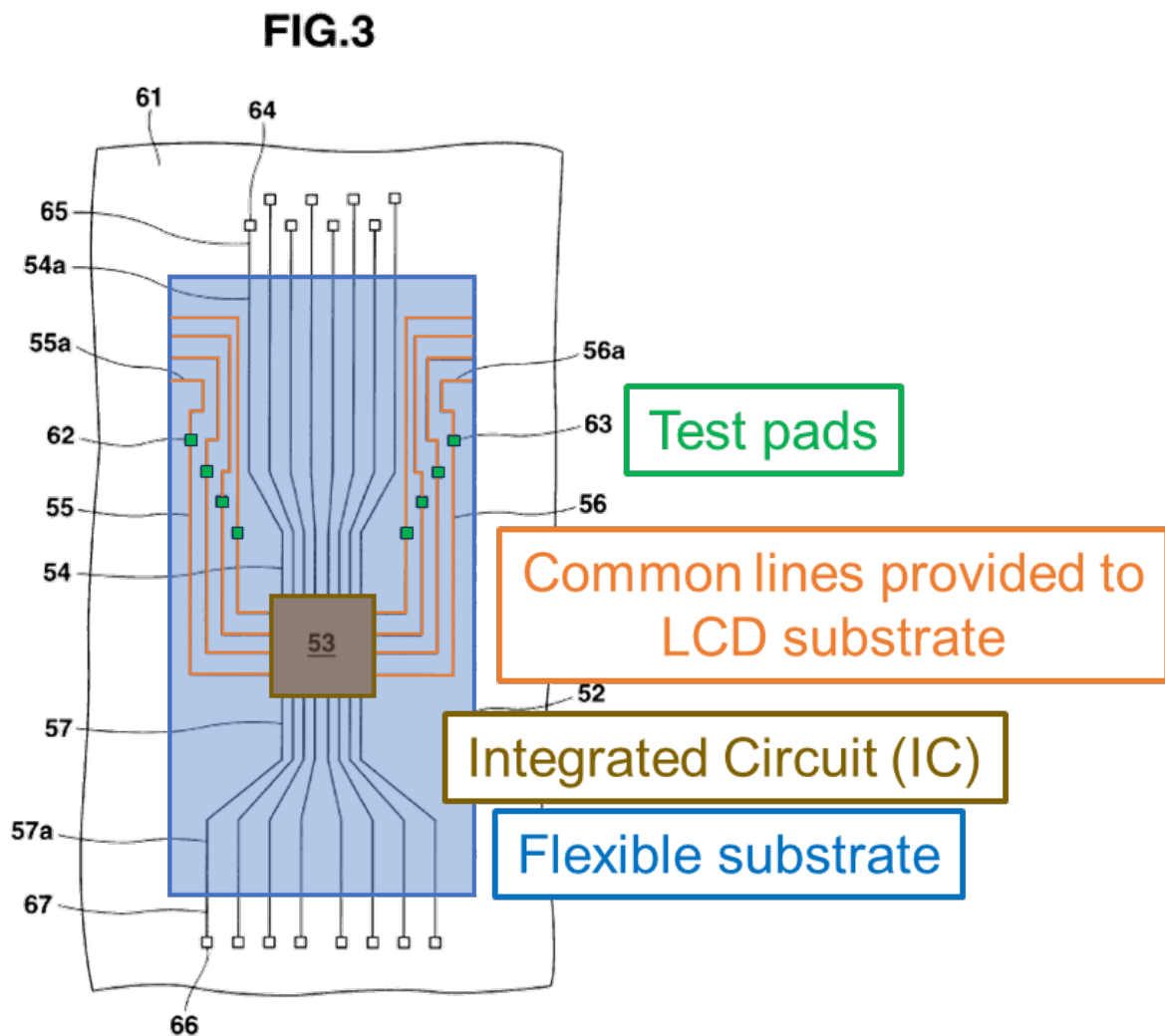
switching that would cause the test pads 62-64 and 66 to output or not output a signal processed in the IC. *See generally* Ex. 1004. Her fails to fill that gap, as I explain below.

51. In my opinion, a POSITA would not modify Saito in view of Her to obtain the claimed “switching section” because doing so would render Saito largely inoperable. In particular, Saito teaches test pads on wires that supply signals to the LCD array substrate. *E.g.*, Ex. 1004, Figs. 1, 2.

52. More specifically, the test pads that Dr. Tentzeris identifies as being “capable of outputting a signal processed in the integrated circuit” for claim 1[e]—test pads 62 and 63—are on wires 55 and 56 as taught by Saito. *See* Ex. 1002, ¶ 88; Ex. 1004, Fig. 3. Saito describes these wires as “output lead wires 55 and 56 for the common terminals.” Ex. 1004, 4:18-21. Saito further describes output lead terminal portions 55a and 56a “for the common electrodes.” *Id.*, 4:45-52. And Saito teaches that the output lead terminals 55a and 56a are “connected to . . . the common terminals 36 and 37 of the liquid crystal display panel 31 via anisotropic conductive adhesive.” *Id.*, 4:58-63. A POSITA would understand that the wires 55 and 56 therefore supply the common signals or, equivalently, scan line signals to the LCD panel.

53. I have annotated Saito’s Figure 3 below to emphasize that the **common lines** output from the **integrated circuit** do not terminate at the **test pads**,

but rather continue through to the terminals at the edge of the flexible substrate, where they connect to the LCD panel and supply the common lines as evident from Dr. Tentzeris's annotated Figure 2 of Saito.



Ex. 1004, Fig. 3 (annotations added).

FIG.2A

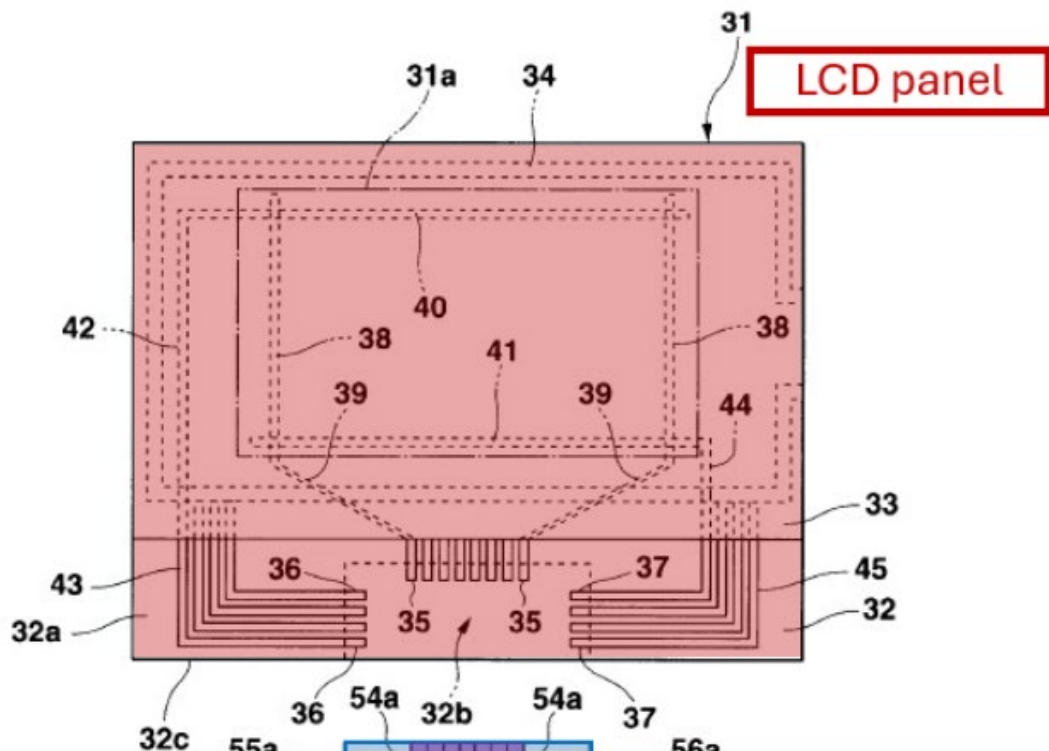
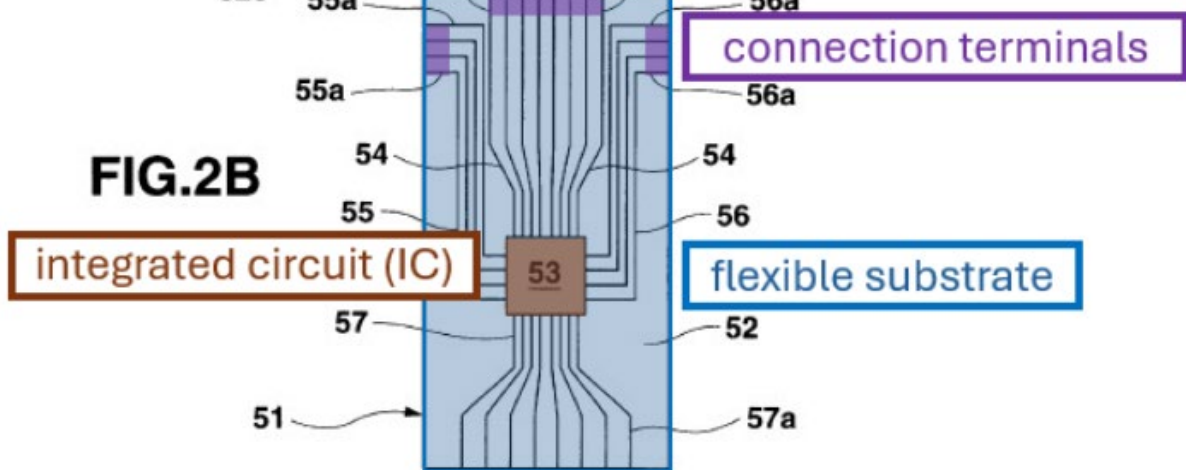


FIG.2B



Ex. 1002, p. 21.

54. A POSITA would further understand that these common or scan lines are necessary to the fundamental operation of the LCD pixels.³ If the scan lines are in an off state, the pixels cannot function and the row will be dark.

55. Dr. Tentzeris opines that “a POSITA thus would be motivated to add the on/off switching mechanism taught in Her to selectively enable or disable the connection between the test pad and the driver IC” in Saito. Ex. 1002, ¶ 98. I disagree. If the “connection between the test pad and driver IC” in Saito is disabled, the driver IC cannot drive the corresponding scan line or row of counter electrodes in the LCD panel. This is so because Saito’s test pad, which Dr. Tentzeris equates to an “inspection electrode,” is directly connected to the output lead terminal portions 55a and 56a, which supply the common electrodes on the LCD panel as I explained above and illustrated with my annotated version of Saito’s Figure 3. Because Saito’s test pad is directly connected to the output terminal, the two *cannot be operated independently*: that is, the connection

³ In an active-switching LCD device, the gate terminals of one row of switching TFTs (thin film transistors) are common to all TFTs in the row. For this reason, the associated electrodes controlling rows of TFTs can be referred to as common electrodes. Similarly, in a passive LCD device, the common electrodes are electrically floating except for one common electrode that is at a fixed potential, typically the ground potential. At the intersections of the grounded common electrode and the segment electrodes (which carry the image information), an electric field is generated that orients the liquid crystal molecules in each pixel, thereby giving the associated pixels the desired transparency.

between the test pad and the driver IC cannot be selectively disabled as Dr. Tentzeris proposes without also disabling the output lead terminal portions 55a and/or 56a for the common electrodes.

56. In my opinion, a POSITA would understand that the coupling (i.e. connection) of the test pad to the signal line in Saito precludes the possibility for the “inspection electrode” to be turned “on / off” in the manner that the Dr. Tentzeris proposes. In the test mode, the “inspection electrode” cannot be turned “off” because the test pad provides a testing signal. Similarly, in the normal mode, the input / output lines and the connected “inspection electrode” cannot be turned “off” because the input / output lines provide necessary signals to the LCD panel. Accordingly, the configuration that results from the combination of Saito and Her cannot meet the claim limitation.

57. Dr. Tentzeris identifies several purported advantages of incorporating Her’s switching functionality into Saito’s test pads, including reducing parasitic capacitance and improving power efficiency. Ex. 1002, ¶ 98. In my opinion, however, each of these purported advantages would be substantially outweighed by the disadvantage of compromising the basic operation of the LCD panel itself. While a consumer might derive some small benefit from corresponding noise reduction and power savings, an LCD panel manufacturer would not be motivated to add switching circuitry to reduce parasitic capacitance and improve power

efficiency where doing so would also require shutting down entire rows of pixels. Shutting off rows of pixels would fundamentally compromise the basic operation of Saito's LCD panel, leading to unacceptable linear artifacts in any rendered image.

58. Similarly, Dr. Tentzeris opines that a POSITA would know that isolating the test pad "when it is not needed" would reduce the risk of electro-static discharge, current leakage, or other factors affecting the IC. Ex. 1002, ¶ 98. In my opinion, however, a POSITA would understand that Saito's LCD device does not have periods during which the common lines are 'not needed' and could be shut down to avoid carrying signals processed in the integrated circuits. Disabling the common lines by not outputting a signal processed in the integrated circuit would again compromise the basic operation of Saito's LCD device.

59. In summary, in my opinion, a POSITA would not be motivated to combine Saito and Her because incorporating Her's switching functionality into Saito would destroy basic functioning of Saito's LCD panel. In my opinion, therefore, Saito in view of Her cannot teach this claim limitation.

2. *Claim 8[f]: “a switching section that switches the types of signals that are to be output from the inspection electrode”*

60. In my opinion, Saito in view of Her does not disclose or render obvious “a switching section that switches the types of signals that are to be output from the inspection electrode” either. Ex. 1001, claim 8[f].

61. In his declaration, Dr. Tentzeris relies for claim element 8[f] on his discussion of claim 3, which depends from claim 1 and recites “[t]he flexible substrate according to claim 1, wherein the switching section that [*sic*] switches the types of signals that are to be output from the inspection electrode.” Ex. 1002, ¶ 126; Ex. 1001, 10:61-63. In responding to Dr. Tentzeris, I therefore address his opinions concerning claim 3 in Ground 1, which he sets forth at paragraphs 104 to 107 of his declaration.

62. To start, I understand that the Petition and Dr. Tentzeris point exclusively to Her as allegedly teaching this limitation. Neither points to Saito as teaching “a switching section that switches the types of signals that are to be output from the inspection electrode.” I disagree with Dr. Tentzeris that Her teaches this limitation, and in my opinion, the combination of Saito and Her therefore cannot teach it either.

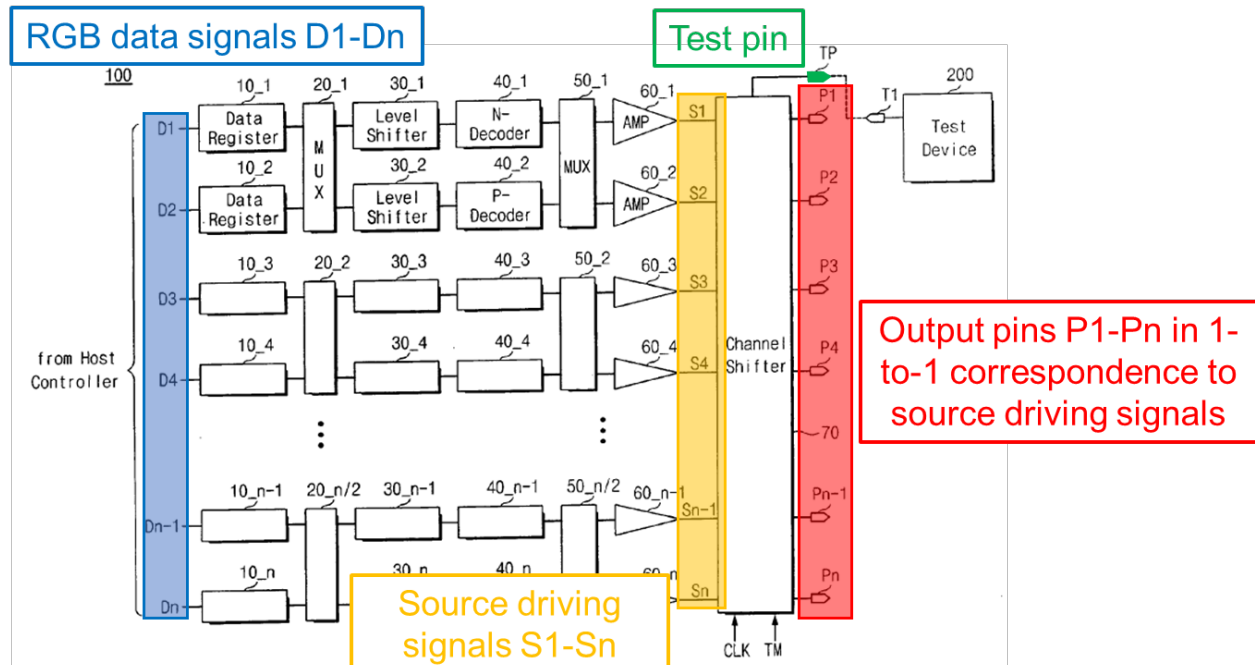
63. The ’512 patent provides non-limiting examples of different “types” of signals that can be output from the inspection electrode, including “a clock

signal, a start signal and a timing signal.” Ex. 1001, 8:44-46. In my opinion, these different signal types are conventional and consistent with a POSITA’s understanding of the term “types of signals” as of the patent priority date.

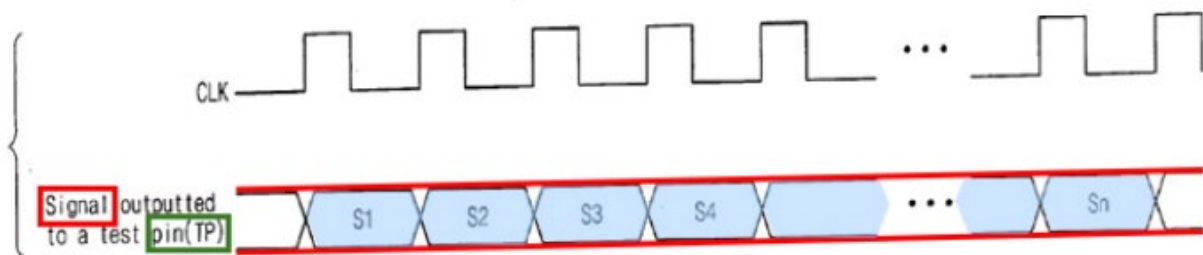
64. Her does not teach different “types of signals” that can be switched between. On the contrary, Her teaches only one signal “type”: a “source driving signal.” More specifically, these “source driving signals” are simply the “RGB data signals D1-Dn” passed through multiplexers, level shifters, decoders, and amplifiers and ultimately provided either to the test pin or to the output pins P1-Pn through the switching section depending on whether the test mode signal is high (on) or low (off). *See* Ex. 1007, ¶ [0023], Fig. 2.

65. I have annotated Her’s Figure 2 below to emphasize that Her teaches providing only one signal type, **source driving signals**, to the channel shifter and therefore to either (1) **output pins P1-Pn** or (2) the **test pin**, depending on whether the test mode is on or off. As is clear from the figure, Her teaches only **RGB data signals D1-Dn** input to the data registers. Following processing in the IC, only one type of signal—**source driving signals S1-Sn**—are output from the amplifiers and subsequently input to the channel shifter. Depending on whether the test mode is on or off, those **source driving signals S1-Sn** are either provided sequentially to the **test pin** (as further shown in Dr. Tentzeris’s annotated Figure 4 below), or placed

on output pins P1-Pn, which Her describes as having one-to-one correspondence to source driving signals S1-Sn. Ex. 1007, ¶ [0031].



Ex. 1007, Fig. 2 (annotations added).



Ex. 1002, p. 51.

66. To be clear, Her's source driving signals all have the same role or function: as Her explains, "[s]ignals S1-Sn outputted from the amplifiers 60_1-60_n are provided to a pixel of a corresponding LCD panel (not shown) through

data output pins P1-Pn acting as source driving signals.” Ex. 1007, ¶ [0028]. Each source driving signal provides a voltage to a pixel on the LCD panel to control RGB color, consistent with the origin of the source driving signals as “RGB data signals D1-Dn.” Her teaches switching the output of the source driving signals between the output pins P1-Pn and the test pin:

In a normal mode, the source driving signals S1-Sn outputted from the amplifiers 60_1-60_n are provided to the LCD panel through the data output pins P1-Pn. However, during a test mode, the source driving signals S1-Sn outputted from the amplifiers 60_1-60_n are outputted through a channel shifter 70 to a test pin TP.

Id. But Her does not teach switching the *types* of signals output from the switching section, as the plain language of claim 8[f] requires. Regardless of their destination (output pins P1-Pn or the test pin), Her’s signals are all source driving signals, that is, signals that control the voltage on the pixel electrodes on the LCD panel. Furthermore, Dr. Tentzeris does not propose to modify Her and doing so would not be obvious in any event, because a POSITA would understand that a shift-register shifts only one type of signal from register to register.

67. Dr. Tentzeris opines that a POSITA would understand the signals output from different amplifiers corresponding to different output channels to be “distinct signal types.” Ex. 1002, ¶ 106. Dr. Tentzeris appears to be saying that regardless of whether source driving signals are provided to the output pins P1-Pn or to the test pin, any two signals that come from neighboring amplifiers (60_1 to

60_*n*) are signals of distinct types. I disagree. A POSITA would have understood that different types of signals might be provided from an IC mounted on a flexible substrate to an LCD panel, including source driving signals, gate driving signals, power signals, and clock signals, consistent with the examples expressly provided by the '512 patent. But a POSITA would not understand two otherwise identical signals output from neighboring amplifiers to be signals of different “types,” simply because they are output from different channels. Indeed, Her’s image data output pins P1 to Pn all provide the same type of signal, specifically image data signals.

68. In my opinion, therefore, Saito in view of Her does not render obvious claim 8. In particular, as I have already discussed at length, neither asserted reference—and thus, no asserted combination—discloses a key aspect of the claimed inventions: a switching section that switches the *types* of signals that are to be output from the inspection electrode.

3. *Claim 9[e]: “a switching section that switches types of the signal, are to be outputted from the inspection electrode”*

69. In my opinion, Saito in view of Her does not disclose or render obvious “a switching section that switches types of the signal, are [*sic*] to be outputted from the inspection electrode” either. Ex. 1001, claim 9[e]. Saito in view of Her does not disclose or render obvious this limitation for the same reasons I

described for the nearly identical claim 8[f] above. I incorporate that discussion here.

70. In my opinion, Saito in view of Her does not render obvious claim 9.

71. In particular, neither asserted reference—and thus, no asserted combination—discloses a key aspect of the claimed inventions: a switching section that switches types of the signal, are [sic] to be outputted from the inspection electrode.

4. *Claims 2-4, and 6*

72. Claims 2-4 and 6 are dependent claims that depend from independent claim 1.

73. Because the Petition cannot show that Saito in view of Her renders obvious claim 1, the Petition cannot show that the combination renders obvious any of claims 2-4 or 6, which depend from claim 1.

74. Finally, I note that neither Dr. Tentzeris nor the Petition can show that Saito in view of Her renders obvious claim 3, for the reasons I discussed at ¶¶ 49-59, *supra*.

VII. ANALYSIS OF TAGUCHI IN VIEW OF HER (GROUND 4)

A. Overview of Taguchi

75. I have reviewed the Taguchi reference and summarize certain aspects of its disclosure here. U.S. Patent Application No. 2004/0183985 is titled “Liquid

Crystal Display Apparatus.” Unlike the ’512 patent, which is directed to efficient placement and operation of an inspection electrode on a flexible substrate, Taguchi is chiefly concerned with wiring continuity across multiple insulation film substrates that supply signals to an LCD panel via drive ICs mounted thereon. *See* Ex. 1006 (Taguchi), Abstract.

76. Taguchi observes that in conventional systems, when no dedicated input-signal substrate (Taguchi’s prior art “Y substrate 3”) is connected, it becomes difficult to confirm whether specific input signal wires, such as the gate or source transmission lines, are properly functioning. Ex. 1006, ¶¶ [0022], [0023], Fig. 1. Taguchi’s proposed solution is to provide a “through wire”—a conductive line that runs between terminals of the insulation-film substrate—and to place a test pad on the through wire. *Id.*, ¶¶ [0026], [0054]. Taguchi’s test pad facilitates measurement of the resistance of the wire or the presence of continuity along the path. *Id.*, ¶ [0066]. The test pad is connected to the through wire, which in turn bridges multiple terminals on the substrate. *Id.*, ¶ [0054], Fig. 5.

77. Taguchi separately describes a prior art configuration including a test pad on the output side of a gate drive IC. Ex. 1006, ¶ [0012], Fig. 2. According to Taguchi, the prior art taught that “the output side signal can be detected through contact of the test pad 9 with the test probe.” *Id.*, ¶ [0012].

78. Unlike the '512 patent, Taguchi is therefore primarily directed to testing for panel-wiring continuity in electro-optical devices that lack a signal-input substrate along at least one side of the LCD substrate. Taguchi is not directed to enabling inspection of IC-generated signals from an IC mounted on a flexible substrate.

B. The teachings of Taguchi in View of Her do not satisfy all elements of claims 1-6 or 8 of the '512 patent.

1. *Claim 1[f]: “a switching section that switches an operation of the inspection electrode on/off to cause the inspection electrode to output or not to output the signal processed in the integrated circuit”*

79. In my opinion, Taguchi in view of Her does not disclose or render obvious “a switching section that switches an operation of the inspection electrode on/off to cause the inspection electrode to output or not to output the signal processed in the integrated circuit.” Ex. 1001, claim 1[f].

80. To start, I understand that the Petition and Dr. Tentzeris concede that the asserted lead reference, Taguchi, does not disclose the “switching section” recited in claim 1[f]. Ex. 1002, ¶ 187; Pet., 72. I agree—Taguchi does not describe any switching that would cause its test pad 9 to output or not output a signal processed in the IC. *See generally* Ex. 1006. Her fails to fill that gap, as I explain below.

81. In my opinion, a POSITA would not modify Taguchi in view of Her to obtain the claimed “switching section” because doing so would render Taguchi largely inoperable.

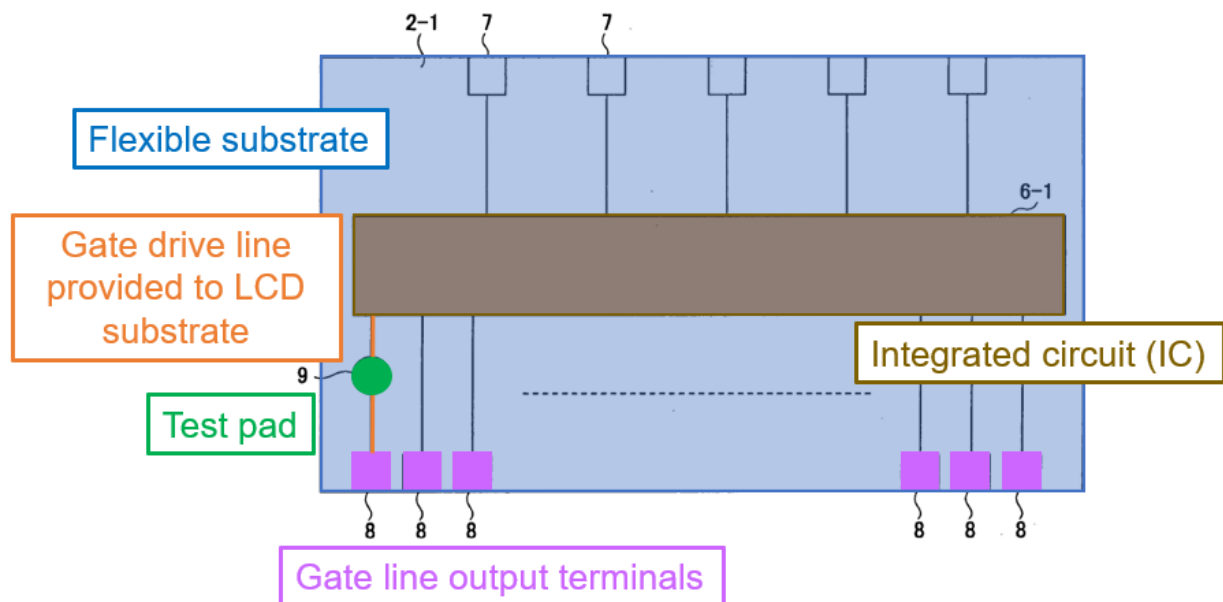
82. The bases for my opinion are similar to those I described for claim 1[f] in Ground 1, at § VI.C.1 *supra*. Like Saito, Taguchi’s prior art test pad 9, as shown in Figure 1, is on a wire that supplies signals to the LCD array substrate. More specifically, the test pad that Dr. Tentzeris identifies as being “capable of outputting a signal processed in the integrated circuit” for claim 1[e]—test pad 9 (*see* Ex. 1002, ¶¶ 82-83)—is on “one of the patterned wires connecting between the output signal terminals 8 and the gate drive IC 6-1.” Ex. 1006, ¶ [0010], Fig. 2. The output signal terminals 8 are located on one of Taguchi’s “insulation film substrates,” 2-1. *Id.*, Fig. 2, ¶ [0010]. Taguchi further teaches that “[a] plurality of insulation film substrates 2-1 through 2-3 . . . are coupled to . . . Y directional edges of a liquid crystal panel 1 in accordance with the form of an active matrix substrate.” *Id.*, ¶ [0007]. Finally, Taguchi teaches:

A Y substrate 3 is connected as a signal input substrate to the insulation film substrates 2-1 through 2-3 having respective gate drive ICs to supply an X axis (horizontal) directional signal. From the Y substrate 3, an input signal is supplied to the insulation film substrates 2-1 through 2-3.

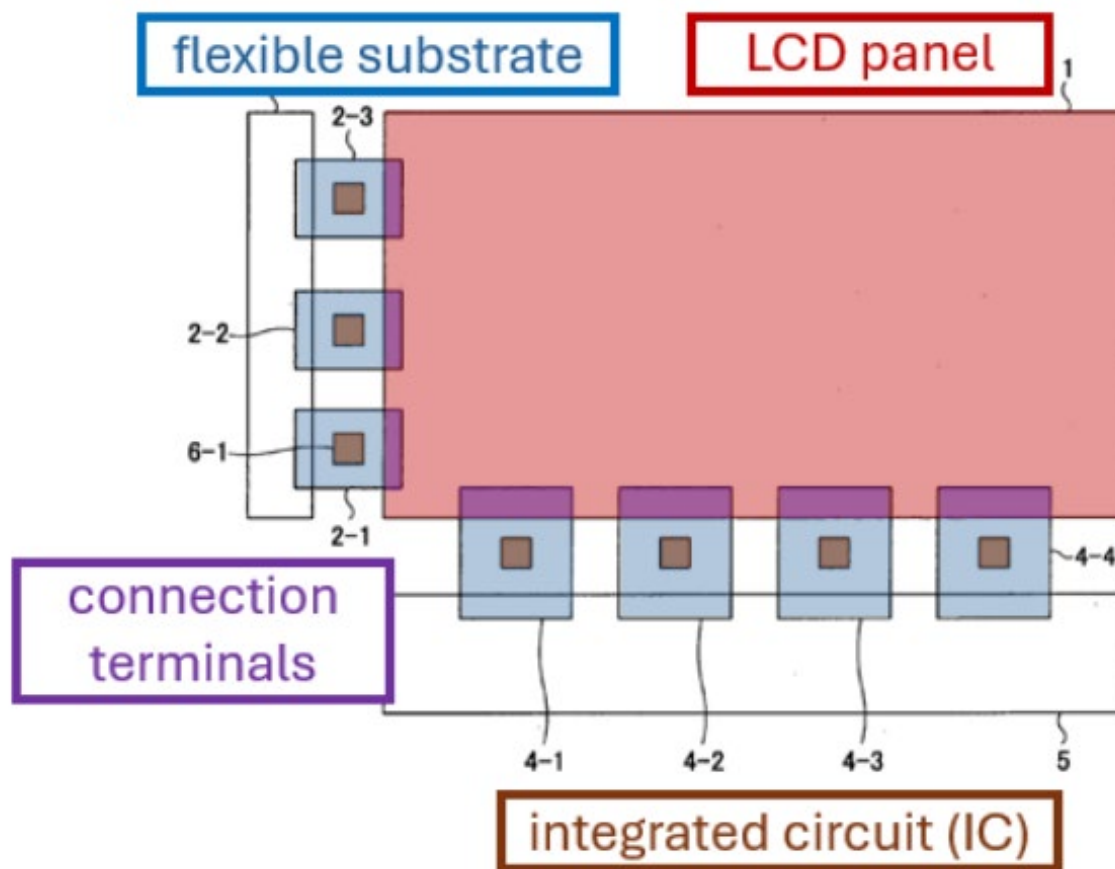
Id., ¶ [0008].

83. In view of these teachings, a POSITA would understand that Taguchi's "output signal terminals 8" on the insulation film substrate connect to corresponding input terminals on the LCD substrate and supply gate signals (horizontal directional signals from the gate drive ICs) to the transistors along each (horizontal) row of the LCD pixel array.

84. I have annotated Taguchi's Figure 2 below to emphasize that the gate drive line output from the integrated circuit and connected to Taguchi's test pad does not terminate at the test pad but instead continues through to one of the gate line output terminals, from which it connects to Taguchi's LCD panel as evident from Dr. Tentzeris's annotated Figure 1 of Taguchi.



Ex. 1006, Fig. 2 (annotations added).



Ex. 1002, p. 81.

85. A POSITA would further understand that these gate signals are necessary to the fundamental operation of the LCD pixels. If a gate signal line is inactive, for example, then no pixels in the row can be switched on. The pixels would be stuck in an off state and the row would be dark.

86. Dr. Tentzeris opines that “it would be obvious to a POSITA in view of Taguchi to connect a patterned wire with an enlarged test electrode to the ‘test pin TP’ of Her for ‘easier reading’,” and further that “[w]hen so connected, the switching mechanism of ‘channel shifter 70’ turns the inspection electrode on the

substrate on/off in response to whether the test mode signal TM indicates the ‘test mode’ . . . or the ‘normal mode’.” Ex. 1002, ¶ 189. I disagree with Dr. Tentzeris that a POSITA would have been motivated to implement Her’s switching mechanism in Taguchi’s inspection electrode on the insulation film substrate. Doing so would fundamentally compromise the basic operation of Taguchi’s electro-optical device. This is so because Taguchi’s test pad, which Dr. Tentzeris equates to an “inspection electrode,” is directly connected to the output signal terminal 8, which supplies the gate signal to rows on the LCD panel, as I explained above and illustrated with my annotated version of Taguchi’s Figure 2. Because Taguchi’s test pad is directly connected to the output signal terminal, the two *cannot be operated independently*: that is, the connection between the test pad and the driver IC cannot be selectively disabled as Dr. Tentzeris proposes without also disabling the output signal terminal 8. If the output signal terminal is disabled, any corresponding rows of pixels on the LCD panel will go dark. A POSITA would find this compromised operation unacceptable.

87. In my opinion, a POSITA would understand that the coupling (i.e. connection) of the test pad to the signal line in Saito precludes the possibility for the “inspection electrode” to be turned “on / off” in the manner that the Petition proposes. In the test mode, the “inspection electrode” cannot be turned “off” because the test pad provides a testing signal. Similarly, in the normal mode, the

input / output lines and the connected “inspection electrode” cannot be turned “off” because the input / output lines provide necessary signals to the LCD panel.

Accordingly, the configuration that results from the combination of Taguchi and Her cannot meet the claim limitation.

88. As he did in Ground 1 for the Saito/Her combination, Dr. Tentzeris identifies several purported advantages of incorporating Her’s switching functionality into Taguchi’s test pad, including reducing parasitic capacitance and improving power efficiency. Ex. 1002, ¶ 190. In my opinion, however, each of these purported advantages would be substantially outweighed by the disadvantage of compromising the basic operation of the LCD panel itself. While a consumer might derive some small benefit from corresponding noise reduction and power savings, an LCD panel manufacturer would not be motivated to add switching circuitry to reduce parasitic capacitance and improve power efficiency where doing so would also require shutting down entire rows of pixels. Shutting off rows of pixels would fundamentally compromise the basic operation of Taguchi’s LCD panel, leading to unacceptable linear artifacts in any rendered image.

89. Similarly, Dr. Tentzeris opines that a POSITA would know that isolating the test pad “when it is not needed” would reduce the risk of electro-static discharge, current leakage, or other factors affecting the IC. Ex. 1002, ¶ 98. In my opinion, however, a POSITA would understand that Taguchi’s LCD device does

not have periods during which the common lines are ‘not needed’ and could be shut down to avoid carrying signals processed in the integrated circuits. Disabling the common lines by not outputting a signal processed in the integrated circuit would again compromise the basic operation of Taguchi’s LCD device.

90. In summary, in my opinion, a POSITA would not be motivated to combine Taguchi and Her because incorporating Her’s switching functionality into Taguchi would destroy basic functioning of Taguchi’s LCD panel. In my opinion, therefore, Taguchi in view of Her cannot teach this claim limitation.

2. *Claim 8[f]: “a switching section that switches the types of signals that are to be output from the inspection electrode”*

91. In my opinion, Taguchi in view of Her does not disclose or render obvious “a switching section that switches the types of signals that are to be output from the inspection electrode” either. Ex. 1001, claim 8[f], for largely the same reasons I already discussed in Ground 1 at § VI.C.2, *supra*.

92. In his declaration, Dr. Tentzeris relies for claim element 8[f] on his discussion of claim 3, which depends from claim 1 and recites “[t]he flexible substrate according to claim 1, wherein the switching section that [*sic*] switches the types of signals that are to be output from the inspection electrode.” Ex. 1002, ¶ 218; Ex. 1001, 10:61-63. In responding to Dr. Tentzeris, I therefore address his

opinions concerning claim 3 in Ground 4, which he sets forth at paragraphs 195 to 198 of his declaration.

93. To start, I understand that the Petition and Dr. Tentzeris point exclusively to Her as allegedly teaching this limitation. Neither points to Taguchi as teaching “a switching section that switches the types of signals that are to be output from the inspection electrode.” I disagree with Dr. Tentzeris that Her teaches this limitation, and in my opinion, the combination of Taguchi and Her therefore cannot teach it either.

94. I explained in § VI.C.2 that the ’512 patent provides non-limiting examples of different “types” of signals that can be output from the inspection electrode, including “a clock signal, a start signal and a timing signal.” I incorporate that discussion by reference here.

95. I also explained in § VI.C.2 that, unlike the ’512 patent, Her teaches only one signal “type”: a “source driving signal.” More specifically, Her’s source driving signals cannot be signals of different types because they all have the same role or function. I incorporate that discussion by reference here as well.

96. As I explained in § VI.C.2, a POSITA would not understand two otherwise identical signals output from neighboring amplifiers to be signals of different “types,” as Dr. Tentzeris opines, simply because they are output from different channels. I incorporate that discussion by reference here as well.

97. In my opinion, therefore, Taguchi in view of Her does not render obvious claim 8. In particular, neither asserted reference—and thus, no asserted combination—discloses a key aspect of the claimed inventions: a switching section that switches the *types* of signals that are to be output from the inspection electrode.

3. *Claims 2-6*

98. Claims 2-6 are dependent claims that depend from independent claim 1.

99. Because the Petition cannot show that Taguchi in view of Her renders obvious claim 1, the Petition cannot show that the combination renders obvious any of claims 2-6, which depend from claim 1.

100. Finally, I note that neither Dr. Tentzeris nor the Petition can show that Taguchi in view of Her renders obvious claim 3, for the reasons I discussed at ¶¶ 79-90, *supra*.

VIII. ANALYSIS OF TAGUCHI AND HER IN VIEW OF SAITO (GROUND 5)

A. The teachings of Taguchi and Her in view of Saito do not satisfy all elements of claim 9 of the '512 patent.

1. *Claim 9[e]: “a switching section that switches types of the signal, are to be outputted from the inspection electrode”*

101. In my opinion, Taguchi and Her in view of Saito does not disclose or render obvious “a switching section that switches types of the signal, are [*sic*] to be

outputted from the inspection electrode” either. Ex. 1001, claim 9[e]. Taguchi in view of Her does not disclose or render obvious this limitation for the same reasons I described for the nearly identical claim 8[f] in Ground 4 above. I incorporate that discussion here. I note that while Ground 5 of the Petition adds an additional reference—Saito—to the Taguchi/Her combination, Dr. Tentzeris does not rely on Saito for any alleged teaching of claim 9[e]. Therefore I do not address Saito here in the context of Ground 5, although I reserve the right to address Saito for Ground 5 should these proceedings be instituted.

102. In my opinion, therefore, Taguchi and Her in view of Saito does not render obvious claim 9.

103. In particular, none of the asserted references—and thus, no asserted combination—discloses a key aspect of the claimed inventions: a switching section that switches types of the signal, are [sic] to be outputted from the inspection electrode.

IX. ANALYSIS OF GROUNDS 2, 3, AND 6

104. I note that Grounds 2, 3, and 6 as raised by the Petition challenge only dependent claims. Ground 2 challenges claim 5, which depends from claim 1. Pet., 52. Ground 3 challenges claims 2 and 7, which depend from claim 1. Pet., 55. Like Ground 3, Ground 6 challenges claims 2 and 7.

105. Because neither the Petition nor Dr. Tentzeris has established that any of these independent claims are obvious in view of any of the asserted references—for the reasons I discussed for Grounds 1, 4, and 5 herein—they cannot show that any of the dependent claims are obvious either.

106. I note further that the Petition and Dr. Tentzeris rely on an additional reference, Kim, for Grounds 3 and 6. Neither the Petition nor Dr. Tentzeris relies on Kim for any of the independent claims, and I therefore do not address Kim here. I reserve the right to address the Kim reference, Petitioner's arguments, and Dr. Tentzeris's opinions concerning Kim should these proceedings be instituted.

X. ADDITIONAL REMARKS

107. I reserve any right that I may have to supplement this declaration if further information becomes available or if I am asked to consider additional information or to submit an additional declaration if *inter partes* review is instituted. Furthermore, I reserve any right that I may have to consider and comment on any additional expert statements and testimony of Petitioner's expert in this matter.

108. I hereby declare that all statements made of my own knowledge are true and that all statements made on information and belief are believed to be true. I further declare that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or

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both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patents issued thereon.

Dated: December 10, 2025



E. Fred Schubert, Ph.D.

APPENDIX A

Curriculum Vitae: E. Fred Schubert

Contact information

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Citizenship

Born in Stuttgart, Germany (1956)
 Naturalized United States Citizen (1995)

Education

University of Stuttgart	Electrical Engineering	Vordiplom	(U. S. equivalent BSEE)	1978
University of Stuttgart	Electrical Engineering	Diplom Ingenieur (Honors)	(U. S. equivalent MSEE)	1981
Oregon State University	Electrical Engineering	Exchange Student		1977–1978
University of Stuttgart	Electrical Engineering	Doktor Ingenieur (Honors)	(U. S. equivalent Ph.D.)	1986

Current appointment

2002 – present: Professor, Department of Electrical, Computer, and Systems Engineering; Rensselaer Polytechnic Institute, Troy NY

Previous appointments

2002 – 2015: Head and Founder of the Future Chips Constellation; Rensselaer Polytechnic Institute
 2002 – 2015: Wellfleet Senior Constellation Professor, Future Chips (Chaired Professor); Rensselaer Polytechnic Institute
 2002 – 2012: Professor Department of Physics, Applied Physics, and Astronomy; Rensselaer Polytechnic Institute
 2008 – 2009: Director, Founding Director, and Principal Investigator, NSF Engineering Center for Smart Lighting, Rensselaer Polytechnic Institute
 2002 – 2003: Adjunct Professor, Boston University
 1995 – 2002: Professor, Boston University, Department of Electrical and Computer Engineering; Director of the Semiconductor Devices Research Laboratory; Affiliated Faculty of the Photonics Center.
 1988 – 1995: Member of Technical Staff; Principal Investigator; and Member of Management at AT&T Bell Laboratories in Murray Hill, New Jersey
 1985 – 1987: Post-Doctoral Member of Technical Staff at AT&T Bell Laboratories in Holmdel, New Jersey.
 1981 – 1985: Scientific Member of Staff in the Department of Solid-State Chemistry at the Max Planck Institute for Solid-State Research in Stuttgart, Germany. Ph.D. Dissertation title: “Modern Schottky gate field-effect transistors based on III–V semiconductors”

Fields of Technical Expertise, Hands-on Experience, and Teaching

- Expertise, hands-on experience, and teaching in semiconductor opto-electronics including the following devices: LED, semiconductor laser, vertical cavity surface-emitting laser (VCSEL), solar cell, photo-detector, LED displays, micro-LED displays, LCD displays, and OLED displays. The activities include the design, fabrication, processing, and packaging of the devices, and the use of the devices in circuits and systems. (1981 to present)
- Expertise, hands-on experience, and teaching in semiconductor electronics including the following devices: MESFET, HFET, MOSFET, CMOS-FET, LDD MOSFET, LD MOS FET, FinFET, GAA FET, Vertical MOSFET (high-power MOSFET), thyristor, GTO thyristor, and IGBT. The activities include the design, fabrication, processing, and packaging of the devices, and the use of the devices in discrete and integrated circuits. (1979 to present)
- Expertise, hands-on experience, and teaching in thin-film deposition of metal, semiconductor, and insulator films by PVD (physical vapor deposition) and CVD (chemical vapor deposition) including PECVD (plasma enhanced CVD), MOCVD (metal-organic CVD), ALE (atomic layer epitaxy), ALD (atomic layer deposition), and bulk crystal growth (AlN, GaN, and sapphire). Epitaxial growth of silicon, III-V arsenide, phosphide and nitride epitaxial layers on GaAs, sapphire, Si, and GaN substrates by epitaxy including molecular beam epitaxy (MBE),

metal-organic chemical vapor deposition (MOCVD), and vapor-phase epitaxy (VPE). High-k materials, low-k-materials, phosphors, resins, polymers, encapsulants, alloy semiconductors and their deposition technologies such as epitaxy, CVD, and PVD. Doping of semiconductors by various means including delta doping and atomic monolayer doping. (1981 to present)

- Expertise, hands-on experience, and teaching in the design, operation, and usage of semiconductor devices in lighting systems, communication systems, and power-supply systems and in the analysis and development of LED power supplies using Boost and Buck Converters. (1993 to present)

Technical Research Activities

- Design, development and fabrication of a Si pressure sensor based on the piezo-resistivity of Si using a bridge configuration of four thin-film Si resistors (1979 – 1980)
- Design of a electro-optic Mach-Zehnder Interference Modulator based on Lithium niobate (LiNbO_3) operating at a wavelength of 1300 nm (1980 – 1981)
- First study of hot electron effects in selectively doped $\text{Al}_x\text{Ga}_{1-x}\text{As}/\text{GaAs}$ heterostructures (1983)
- Demonstration and elimination of parallel conduction in $\text{Al}_x\text{Ga}_{1-x}\text{As}/\text{GaAs}$ heterostructures (1984)
- First analysis of semiconductors doped with simultaneously shallow and deep donors (1984).
- Development and use of thyristor circuits (including GTO thyristor circuits) for the control of a lamp heating system (1984 – 1985)
- Proposal and demonstration of the δ -doped field-effect transistor. Short-channel effects in sub-micron field-effect transistors can be reduced to their theoretical minimum by using δ -doped structures (1985)
- Development of the theory of alloy broadening in luminescence spectra of alloy semiconductors such as $\text{Al}_x\text{Ga}_{1-x}\text{As}$. The current understanding of the low-temperature spectral linewidths of ternary and quaternary alloy semiconductors is based on this theoretical model. The publication analyzing the phenomenon of alloy broadening has been referenced far in excess of 100 times (1984)
- First demonstration of a light-emitting diode with a doping superlattice active region (1985)
- Application of δ -doping to selectively doped heterostructures; Demonstration of high-electron-mobility transistors (HEMTs) with highest free electron concentrations; Analysis of structures by SEM, TEM, and SIMS (1986).
- Demonstration of delta-doped non-alloyed ohmic contacts with very low contact resistance and subsequent demonstration of self-aligned field-effect transistor with delta-doped non-alloyed ohmic contacts (1986)
- Demonstration of the spatial localization of dopants within 20 Å for a number of doping elements in delta-doped semiconductors including GaAs and Si for MESFET and lightly-doped drain (LDD) MOSFET applications and the analysis of delta-doped structures by SIMS (secondary ion mass spectrometry) (with colleague Henry S. Luftman, 1983-1995)
- Significant improvement of the optical properties of doping superlattices by employment of delta doping. Improvement is demonstrated by the first observation of quantized interband transitions in the absorption (1988) and in the emission spectra (1989)
- First demonstration of tunable doping superlattice laser (1989)
- First quantitative analysis of the capacitance-voltage (CV) profiling technique in semiconductors with quantum-confined carriers. Demonstration that resolution of CV profiles in quantum-confined semiconductors is not limited to the Debye screening length (1990)
- Invention and demonstration a new concept by which heterojunction band discontinuities occurring between two different semiconductors are eliminated. The *elimination of heterojunction barriers* is based on parabolic compositional grading of doped heterojunctions. This concept is widely used in the fabrication of vertical cavity surface emitting lasers and other heterojunction devices (1991)
- Invention and first demonstration of resonant cavity light-emitting diode (RCLED) which uses photon quantization in microcavities to enhance the spontaneous emission properties (1992)
- Demonstration of giant enhancement of luminescence intensity in Er-doped Si-SiO_2 microcavities (1992)
- First demonstration of a resonant-cavity detector which is useful for wavelength-selective detection (1993)
- Demonstration of resonant-cavity light-emitting diode (RCLED) with very high brightness. The experimental brightness of the RCLED is five times higher than that of conventional LEDs. Based on calculations, the brightness of RCLEDs is expected to exceed that of conventional LEDs by more than a factor of ten (1994)
- Demonstration of delta doping in silicon for the fabrication of shallow junctions in scaled-down Si lightly-doped drain (LDD) MOSFETs for integrated circuits (Si ICs) (with colleague Dr. H. J. Gossmann, 1990 – 1995)
- Invention of a new concept, *superlattice doping*, for enhanced p-type doping of GaN. All acceptors in GaN are deep, resulting in a low electrical acceptor activation of only 5 %. The new concept of superlattice doping is expected to increase the electrical activation of acceptors by more than a factor of ten (with post-doctoral associate Dr. W. Grieshaber, 1995)

- Investigation of yellow luminescence in GaN and the use of microcavity effects in Ag / GaN / sapphire structures to determine the refractive index of GaN (with post-doctoral associate Dr. W. Grieshaber, 1996)
- Demonstration of the first GaN / GaInN double heterostructure laser. The laser has cleaved facets and was optically pumped. Laser action was demonstrated by (i) a threshold in the light-versus-current characteristic, (ii) spectral narrowing below kT above threshold, (iii) a TE / TM polarization ratio greater than one hundred above threshold, and (iv) increased slope efficiency with increasing back-side facet reflectivity (with graduate student D. A. Stocker, 1997)
- Co-inventor of photonic-crystal light-emitting diode, PC-LED, jointly with group of Prof. John D. Joannopoulos at MIT (publication by Shanhui Fan *et al.* appeared in *Physical Review Letters* in 1997; US patent 5,955,749 was issued in 1999)
- First demonstration of crystallographic etching of GaN (with graduate student D. A. Stocker, 1998). The discovery, crystallographic etching, can be implemented by wet chemical etching, including photo-enhanced electrochemical (PEC) wet etching. The discovery is widely used in the LED industry to strongly enhance light extraction from LED chips and is found in LED light bulbs.
- Experimental demonstration of a ten-fold enhancement of p-type doping activation in $\text{Al}_x\text{Ga}_{1-x}\text{N}$ /GaN doped superlattices as compared to bulk GaN and $\text{Al}_x\text{Ga}_{1-x}\text{N}$ (with graduate students D. A. Stocker and I. D. Goepfert, 1999)
- Invention and demonstration of the photon-recycling semiconductor light-emitting diode (PRS-LED) which emits *white* light and many other colors with very high luminous performance of $> 300 \text{ lm/W}$ (with graduate students X. Guo and J. W. Graff, 1999). Invention of the monolithically integrated GaInN/GaN PRS-LED (with graduate students X. Guo and J. W. Graff, 2000)
- Invention and demonstration of polarization-enhanced ohmic contacts in p-type and n-type GaN (with graduate students Y.-L. Li and J. W. Graff 2000)
- Invention and demonstration of AlGaInP light-emitting diode with omni-directional reflector (ODR) for high light extraction efficiency (with post-doctoral associate Th. Gessmann and graduate student J. W. Graff, 2001)
- Developed novel model for high diodes ideality factors ($n \gg 2.0$) in UV LEDs based on multiple rectifying elements (with graduate student J. M. Shah and Prof. Th. Gessmann, 2003)
- Developed new class of materials, low-refractive index materials, or low- n materials, with an unprecedented low refractive index of $n < 1.10$; use of these materials as low- k materials for inter-metal-layer dielectrics in Si lightly-doped drain (LDD) MOSFETs in conjunction with ALD-deposited high- k gate dielectric MOSFETs for integrated circuits (Si ICs) (with Dr. Jong Kyu Kim, "JQ" Xi, Professors Joel Plawsky, Bill Gill, starting in 2003)
- Developed theory for temperature coefficient of forward voltage in light-emitting diodes, particularly UV light-emitting diodes (with graduate student Yangang "Andrew" Xi, Dr. Jong Kyu Kim, and collaborators at Sandia National Laboratories, 2004, 2005)
- Invented highly efficient "remote phosphor configurations" in white light-emitting diodes (with Jong Kyu Kim, Hong Luo, and collaborators at SAIT-Samsung) (2004, 2005)
- Discovered whispering gallery modes in white LEDs with remote phosphors (with graduate student Hong Luo, Jong Kyu Kim, Yangang "Andrew" Xi, and collaborators at SAIT-Samsung, 2005)
- Developed graded-index antireflection coatings that, unlike conventional anti-reflection coatings, have broadband omni-directional characteristics; the graded-index antireflection (AR) coatings use novel low- n materials; the AR coatings can be used for of solar cells, LCD displays, and AMOLED displays (with Jingqun "JQ" Xi, Jong Kyu Kim, 2007)
- Developed efficiency-droop reducing GaInN / GaInN and GaInN / AlGaInN LED active regions grown by MOCVD and ALE that were demonstrated to reduce the efficiency droop by as much as 40% (with Jong Kyu Kim, Martin F. Schubert, Di Zhu, Jiuru Xu, Mary Crawford, and Dan Koleske, starting in 2007)
- Developed analytic model for efficiency droop based on drift-induced reduction of the carrier-injection efficiency (with Guan Bo Lin, Jaehee Cho, and others, 2012)

Honors and awards

- Google Scholar profile, including the Hirsch-index (h-index) can be found at <http://scholar.google.com> > under profile "E. Fred Schubert"
- Elected to *Senior Member* of the *IEEE* "in recognition of professional standing" (1993)
- Recipient of the Literature Prize of the *Verein Deutscher Elektrotechniker (VDE)* for "Doping in III-V semiconductors" (Cambridge University Press, Cambridge, 1993). Citation: "The book concerns all aspects of doping in III-V semiconductors. Fundamental, practical, and technological issues of doping are addressed. The book covers the basic theory of shallow donors, shallow acceptors, deep levels, and their influence on the free carrier concentration. It also discusses doping during growth, epitaxy, diffusion, and ion implantation. In the field of semiconductor devices, the book emphasizes applications requiring highly controlled doping

- distributions. It is an excellent monograph equally suited for study, research, and industry" (1994)
- Elected as a member of the *Bohemian Physical Society* (Cornell University, Ithaca, NY). Citation: "For seminal contributions to the control of spontaneous emission by use of wavelength-size optical cavities, specifically the first demonstration in a glass host using rare earth implanted Si/SiO₂ resonant microcavities" (1994)
 - Listed in "Who's Who In Science And Engineering" and "Who's Who in America" published by *Marquis Who's Who*, publishers of the original *Who's Who in America*. (*Marquis Who's Who*, New Providence, NJ) ISBN 0-8379-5755-9 (1996 – present)
 - Elected Fellow of the *SPIE* "For pioneering research in semiconductor doping and sustained contributions to the development of high-efficiency light-emitting diodes and lasers". According to the Society's bylaws, a Fellow "shall be distinguished through his achievements and shall have made outstanding contributions in the field of optics, or optoelectronics, or in a related scientific, technical, or engineering field" (1999)
 - Recipient of the *Alexander von Humboldt Senior Research Award* of the Alexander von Humboldt Foundation, a Bonn-based non-profit organization promoting the exchange of scientific knowledge between German and highly qualified foreign scholars. According to the Alexander von Humboldt Foundation, academic qualification is the only selection criterion for the award. The award resulted in two extended visits with the Microoptics Laboratory of Professor Jürgen Jahns at the University of Hagen, Germany (1999)
 - Elected to *Fellow of the IEEE* "for contributions to semiconductor doping and resonant-cavity devices". According to the IEEE definition "the grade of Fellow is one of unusual professional distinction conferred by the Board of Directors only upon a person of extraordinary qualifications and experience" (1999)
 - Listed in the "Dictionary of International Biography, 29th Edition" published by the *International Biography Center*, Cambridge, United Kingdom (2000)
 - Recipient of the 2000 *Discover Magazine Award for Technological Innovation* presented by the *Christopher Columbus Foundation* in the category "Energy". The prize was awarded "for the invention and demonstration of the photon recycling semiconductor light-emitting diode", an all-semiconductor LED capable of emitting white light with very high efficiency, see < www.discover.com/awards > (2000)
 - Recipient of the *RD100 Award* of the R&D Magazine that honors the "100 most technologically significant products of the year" (with Klaus Streubel of Osram-Sylvania Corp. and Rickard Marcks von Wurtemberg of Mitel Corp.). The prize was awarded for the "Resonant-cavity light-emitting diode" that uses enhanced spontaneous emission occurring in resonant cavities. The device is used in plastic optical fiber communication links, in telescopes for rifles, and many other applications (2000).
 - Elected to *Fellow of the OSA* "for the invention and demonstration of the resonant-cavity LED and the photon-recycling semiconductor LED". OSA Fellows are elected by the OSA Board of Directors (2001)
 - Recipient of the Boston University Provost Innovation Fund Award (Provost Dennis D. Berkey) valued at \$ 25,000 for research and development of promising technologies (2001)
 - Elected to *Fellow of the APS* "for pioneering contributions to the doping of semiconductors including delta doping, doping of compositionally graded structures resulting in the elimination of band discontinuities, and superlattice doping to enhance acceptor activation" (2001)
 - Honored with RPI Medal as Senior Constellation Chair during Investiture Ceremony (2002)
 - Received "2002 Rensselaer Polytechnic Institute Trustee Faculty Achievement Award" (2002)
 - Inducted as Wellfleet Senior Constellation Professor, Future Chips, Rensselaer Polytechnic Institute, November 21 (November 2003)
 - Distinguished Lecturer of the IEEE Electron Devices Society (2003–2006)
 - Elected member in Eta Kappa Nu (2004)
 - "Best Oral Presentation Award" was won by Ph. D. student Hong Luo (who was the presenter), J. K. Kim, Y. A. Xi, J. M. Shah, Th. Gessmann and E. F. Schubert "Improvement of extraction efficiency of GaInN light-emitting diodes by employment diffuse omni-directional reflectors" *Connecticut Microelectronics & Optoelectronics Consortium (CMOC)*, 14th annual symposium, New Haven CT, March 17 (March 2005).
 - "Best Student Poster Award" of the *International Semiconductor Device Research Symposium (ISDRS)* was won by Ph. D. student J.Q. Xi (presenter), Jong Kyu Kim, Dexian Ye, Jasbir S. Juneja, T.-M. Lu, Shawn-Yu Lin, and E. Fred Schubert "Optical Thin Films with Very Low Refractive Index and Their Application in Photonic Devices", *International Semiconductor Device Research Symposium (ISDRS)*, Dec. 7–9, Bethesda, MD (December 2005)
 - "MRS Silver Award" of the Materials Research Society was won by Ph. D. student Yangang Andrew Xi (who was the presenter), K. X. Chen, F. Mont, J. K. Kim, C. Wetzel, E. F. Schubert, W. Liu, X. Li, J. A. Smart "Extremely high quality AlN grown on (0001) sapphire by using metal-organic vapor-phase epitaxy" *Materials Research Society (MRS) Fall Meeting*, Boston MA, November 27 – December 1 (2006) Boston MA (December 2006)
 - "25 Most Innovative Micro- and Nano-Products of 2007 Award" in July 2007 issue of *R&D Magazine* and *Micro/Nano Newsletter*. This recognition was given for the "Non-Reflective Coating" product that was published in *Nature Photonics* in 2007; full citation: Xi, J.-Q., Martin F. Schubert, J. K. Kim, E. F. Schubert,

Minfeng Chen, Shawn-Yu Lin, Wayne Liu, and Joe A. Smart “Optical thin-film materials with low refractive index for broadband elimination of Fresnel reflection” *Nature Photonics* **1**, 176, March 2007 (July 2007)

- “SCIENTIFIC AMERICAN 50 AWARD” of 2007, as published in the January 2008 issue of *Scientific American*. According to the *Scientific American Magazine*, this award “celebrates visionaries from the worlds of research, industry and politics whose recent accomplishments point toward a brighter technological future for everyone” (January 2008)
- “EDITORS’ CHOICE” of *Science Magazine*, *Science*, Volume **319**, page 1163, February 29 (February 2008). This distinction was awarded for the publication: Jong Kyu Kim et al., “Light-extraction enhancement of GaInN light-emitting diodes by graded-refractive-index indium tin oxide anti-reflection contact” that appeared in *Advanced Materials* **20**, 801, 2008 (February / March 2008)
- Received “2008 Rensselaer Polytechnic Institute Trustee Faculty Achievement Award” (2008)
- “Best Oral Presentation Award” won by David J. Poxson (who was the presenter), Frank W. Mont, Jong Kyu Kim, and E. Fred Schubert “Multilayer nano-structured anti-reflection coating with broad-band omni-directional characteristics” *Connecticut Microelectronics and Optoelectronics Conference (CMOC)*, University of Connecticut, Storrs, Connecticut, April 9 (April 2008)
- “Best Oral Presentation Award” for presentation: David Meygaard, Sameer Chhajed, Jaehee Cho, E. Fred Schubert, Jong Kyu Kim, Daniel D. Koleske, and Mary H. Crawford “Temperature-dependent light-output characteristics of GaInN light-emitting diodes with different dislocation densities” *Connecticut Microelectronics and Optoelectronics Consortium (CMOC) Symposium*, New Haven CT, March 2 (March 2011)
- Identified as top 1% of patentees in the field of optoelectronics by study conducted by Professor Erica Fuchs of Carnegie Mellon University under a study supported by the US National Science Foundation (July 2011)
- Received “2012 Rensselaer Polytechnic Institute Trustee Faculty Achievement Award” (November 2012)
- My “LinkedIn” profile was one of the top 10% most viewed “LinkedIn” profiles during 2012 (January 2013)
- My graduate student, Mr. Ming Ma, received the \$ 30,000.00 Lemelson-Rensselaer Student Prize for the invention entitled “Graded-refractive-index (GRIN) structures for brighter and smarter light-emitting diodes”; The Prize is awarded annually by the Lemelson Foundation (March 2013)
- Received the IEEE Life Fellow Award (2022)

Service to the technical community

- Current or former member of the *American Physical Society* (Member of the *Division of Materials Physics*, Member of the *Division of Condensed Matter Physics*), *Institute of Electrical and Electronics Engineers*, *Materials Research Society*, *Optical Society of America*, *Society for Optical Engineering (SPIE)*, and the *Verein Deutscher Elektrotechniker*
- Co-author of hundreds of research articles, co-inventor of more than 30 United States patents, and numerous foreign patents (1981 – present)
- Gave many invited talks at scientific conferences organized by the *American Physical Society*, *Institute of Electrical and Electronic Engineers*, *Materials Research Society*, *SPIE (The International Society for Optical Engineering)*, *Electrochemical Society*, *American Vacuum Society*, *Engineering Foundation*, and other professional societies (1985 – present).
- Co-editor (with A. M. Glass) of a Special Issue of the *Journal of Optical and Quantum Electronics* (Vol. **22**, 1990) on “Charge-transport assisted optical non-linearities in semiconductors” (1990)
- Symposium chair of the *American Vacuum Society Greater New York and New Jersey Chapter* on “Epitaxially grown semiconductors with atomic level control” (1991).
- Moderator of MRS Internet discussion on “Doping and Dopants in GaN” (*MRS Internet Journal*, 1995 – 1997)
- Member of review panels of the National Science Foundation (1995 – present)
- Conference Chair of SPIE Photonics West conference on “Light-emitting diodes: Research, Manufacturing, and Applications” San Jose, CA (1997)
- Technical work has been featured in popular journals, magazines and newspapers including the *New Scientist*, *Discover Magazine*, *Wall Street Journal*, *Boston Globe*, *Focus*, and on National Public Radio (1996 – present)
- Conference Chair of SPIE Photonics West conference on “Light-emitting diodes: Research, Manufacturing, and Applications” San Jose, CA (1998)
- Program Committee Member: IEEE IEDM, International Electron Devices Meeting (1999 and 2000)
- Conference Chair of SPIE Photonics West conference on “Light-emitting diodes: Research, Manufacturing, and Applications” San Jose, CA (1999)
- Program Committee Member: ISBLLED, International Symposium on Blue Laser and Light-Emitting Diodes, Berlin, Germany, March 5 – 10 (2000)
- Conference Chair of SPIE Photonics West conference on “Light-emitting diodes: Research, Manufacturing, and Applications” San Jose, CA (2000)

- Conference Chair and Co-Organizer of the TMS- and ONR-sponsored conference on “Doping, Dopants, and Low Field Carrier Dynamics in Wide Gap Semiconductors”, Copper Mountain, Colorado, April 2 - 6 (2000)
- Chair, IEEE LEOS, Central New England Chapter. During my tenure as Chair, the Central New England Chapter won the IEEE LEOS Chapter award for the highest membership growth (1999–2000)
- Expert Witness involving semiconductor materials, devices, and packaging including elemental and compound semiconductors such as Si, SiGe, SiC, as well as III–V arsenides, phosphides and nitrides (1998–present)
- Member of the Board of Governors, IEEE Laser and Electro-Optics Society (LEOS) (1999–2000)
- Member of the Optoelectronics Industry Development Association (OIDA) Roadmap Panel on Solid-State Lighting, Albuquerque NM Oct. 26–28 (2000)
- Conference Chair of SPIE Photonics West conference on “Light-emitting diodes: Research, Manufacturing, and Applications” San Jose, CA (2001)
- Panel Member of National Research Council meeting on “Solid-State Lighting:” held at NAS and NAE, Washington DC, March 26 (2001)
- Program Committee Member of SPIE Photonics West conference on “Laser and LED Applications” chaired by Dr. Kurt Linden, San Jose CA Jan (2002)
- Conference Chair of SPIE Photonics West conference on “Light-emitting diodes: Research, Manufacturing, and Applications” San Jose, CA (2002)
- Program Committee Member: ISBLLED, International Symposium on Blue Laser and Light-Emitting Diodes, Cordoba, Spain, March 11–15 (2002)
- Program Committee Member for subcommittee on “Semiconductor lasers and LEDs” for OSA Conference on Lasers and Electro-Optics and Quantum Electronics and Laser Science Conference (CLEO / QELS) (2002–2003) Baltimore MD June 1–6 (2003)
- Reviewer for the National Research Council of report entitled “Partnerships for Solid-State Lighting: Report of a Workshop” authored by the Board on Science, Technology, and Economic Policy. This report is forwarded to the US Congress for the initiation of a national Solid-State Lighting Initiative. (2002)
- Program Committee Member “Lester Eastman conference on high performance devices” University of Delaware, Newark, Delaware, August 6 – 8 (2002)
- Conference Chair of SPIE Photonics West conference on “Light-emitting diodes: Research, Manufacturing, and Applications” San Jose CA (2003)
- OIDA Next Generation Lighting (NGL) Consortium. Member of “Light-Emitting Diode” Committee (2003)
- Program Committee Member, International Semiconductor Device Research Symposium (ISDRS) Washington DC, Dec. 8 – 12 (2003)
- Program Committee Member of “Display and Solid-State Lighting Devices” conference for OSA/IEEE Conference on Lasers and Electro-Optics (CLEO) (2003 – 2004)
- Elected Member of the IEEE Electron Device Society Administration Committee (IEEE AdCom) (2003–2008)
- Conference Chair of SPIE Photonics West conference on “Light-emitting diodes: Research, Manufacturing, and Applications” San Jose CA (2004)
- Program Committee Member “Fourth International Conference on Solid-State Lighting” August 2 – 6 Denver, CO (2004)
- Program Committee Member for the “Blue 2004: Advanced LEDs and Lasers Conference” Hsinchu, Taiwan, May 10–12 (2004)
- Conference Chair of SPIE Photonics West conference on “Light-emitting diodes: Research, Manufacturing, and Applications” San Jose CA (2005)
- Program Committee Member “International Semiconductor Device Research Symposium” December 7 – 9 Washington, DC (2005)
- Chair of “Display and Solid-State Lighting Devices” conference of OSA/IEEE Conference on Lasers and Electro-Optics (CLEO) (2005)
- Best Oral Presentation Award (Presenter: Hong Luo) at *Connecticut Microelectronics & Optoelectronics Consortium* (CMOC), 14th annual symposium, New Haven CT, March 17 (March 2005)
- Conference Chair of MRS Spring meeting “Symposium DD: Solid-State Lighting Materials and Devices” San Francisco, April 17–21 (April 2006)
- Member on the International Advisory Committee of *First International Conference on Display LEDs* (ICDL 2007), Seoul, Korea, January 31 to February 2 (2007)
- Member, Program Committee of *SPIE Photonics West* conference “Light-Emitting Diodes: Research, Manufacturing, and Applications XI” San Jose, CA, January 20 – 25 (2007)
- Program Chair of *SPIE Photonics West* conference “Semiconductor Lasers and LEDs” San Jose, CA, January 20 – 25 (2007)
- Member, Executive Organizing Committee *SPIE Photonics West* conference “LASE 2007” San Jose, CA, January

20–25 (2007)

- Opto Track Chair of *SPIE Photonics West* conference “Semiconductor Lasers and LEDs” San Jose, CA, January 21 –24 (January 2008)
- Member, Program Committee, Light-emitting diodes: Research, Manufacturing, and Applications, SPIE Photonics West 2008, San Jose, California, January 19 – 24 (January 2008)
- Program Committee Member of the 7th International Symposium on Semiconductor Light Emitting Devices (ISSLED-2008) held in Phoenix, Arizona (USA), April 27 – May 2 (April 2008)
- Member, Program Committee, China SSL 2008, Shenzhen Convention & Exhibition Center, China, July 24 – 26 (July 2008)
- Member, Program Committee, International Workshop on Nitride Semiconductors, IWN 2008, Montreux, Switzerland, October 6 – 10 (October 2008)
- Opto Track Chair of *SPIE Photonics West* conference “Semiconductor Lasers and LEDs” San Jose, CA, January 25 – 29 (January 2009)
- Guest Editor of Special Issue on *Solid-State Lighting* published in the *IEEE Journal of Selected Topic in Quantum Electronics*, July / August edition (August 2009)
- Honorable Conference Chair, 6th China International Forum on Solid-State Lighting (China SSL), Shenzhen Convention & Exhibition Center, China, October 14 – 16 (October 2009)
- Program Committee Member, International Conference on Nitride Semiconductors (ICNS), Jeju, South Korea, October 18 – 23 (October 2009)
- Program Committee Member, The Second International Conference on White LEDs and Solid-State Lighting, Taipei, Taiwan, December 13 – 16 (December 2009)
- Editor, *Compound Semiconductors and Energy Applications and Environmental Sustainability*, Materials Research Society (MRS) Symposium Proceedings Volume 1167 (MRS, Warrendale PA, 2009)
- Conference Chair, OPTO, *SPIE Photonics West 2010*, San Francisco, California, January 23 – 27 (January 2010)
- Guest Editor of Special Issue on *Light-Emitting Diodes* published in the *IEEE Transactions on Electron Devices* (January 2010)
- Program Committee Member, *8th International Symposium on Semiconductor Light Emitting Devices (ISSLED)*, Beijing, China, May 16 – 21 (May 2010)
- International Advisory Committee Member of the 16th *Microoptics Conference (MOC’10)* held in Hsinchu, Taiwan, sponsored and endorsed by OSA and IEEE/Photonics Society and organized by National Chiao Tung University, Oct. 31 to Nov. 3 (October 2010)
- Member of Academic Committee of *China Solid-State Lighting Conference (CHINA SSL 2010)* Shenzhen, China, October 14 – 16 (October 2010)
- Conference Co-Chair, OPTO, *SPIE Photonics West 2011*, San Francisco, California, January 22–27 (January 2011)
- Executive Organizing Committee OPTO, *SPIE Photonics West 2011*, San Francisco, California, January 22–27 (January 2011)
- Program Committee Member of conference entitled: “Light-Emitting Diodes: Materials, Devices, and Applications for Solid-State Lighting XV *SPIE Photonics West 2011*, San Francisco, California, January 22–27 (January 2011)
- Member of CLEO Subcommittee 15, entitled “LEDs, Photovoltaics and Energy-Efficient (“Green”) Photonics” for the 2011 Conference on Lasers and Electro-Optics (CLEO), Baltimore, Maryland May 1– 6 (May 2011)
- Member of the Academic Committee of the 8th China International Forum on Solid-State Lighting (CHINA-SSL-2011) Guangzhou November 8–10 (November 2011)
- Program Committee Member of conference entitled: “Light-Emitting Diodes: Materials, Devices, and Applications for Solid-State Lighting XV *SPIE Photonics West 2012*, San Francisco, California, January 21–26 (January 2012)
- Member of CLEO Subcommittee 15, entitled “LEDs, Photovoltaics and Energy-Efficient (“Green”) Photonics” for the 2012 Conference on Lasers and Electro-Optics (CLEO), San Jose, California, May 6–11 (May 2012)
- Member of Academic Committee of the 9th China International Forum on Solid-State Lighting (CHINA SSL 2012), Guangzhou, China, November 5–7, 2012 (November 2012)
- Program Committee Member of conference entitled: “Light-Emitting Diodes: Materials, Devices, and Applications for Solid-State Lighting XVI *SPIE Photonics West 2013*, San Francisco, California, 2–7 February 2013 (February 2013)
- Member of CLEO Subcommittee in the topic area: “Science & Innovation 15: LEDS, Photovoltaics and Energy-Efficient (“Green”) Photonics” for the CLEO 2013 conference, April 28–May 3, 2013 in Baltimore, Maryland (May 2013)
- Member, International Advisory Committee of the International Conference on Advanced Electromaterials (ICAE 2013) held on Jeju Island, Korea, from November 12–15, 2013 (November 2013)

- Program Committee Member, *Solid-State and Organic Lighting (SOLED)*, OSA Topical Meeting, 3–7 November 2013, Marriott Tucson Star Pass, Tucson, Arizona, USA (November 2013)
- Co-Chair, OPTIC International Conference, Chung Li, Taiwan, National Central University, December 5–7, 2013 (December 2013)
- Program Committee Member of conference entitled: “Light-Emitting Diodes: Materials, Devices, and Applications for Solid-State Lighting XVII” *SPIE Photonics West 2013*, San Francisco, California, 1–8 February (2014)
- Publication Committee Member, *5th International Conference on White LEDs and Solid-State Lighting* (White LEDs), Jeju Island, Korea, May 25–28, 2014 (May 2014)
- Sub-Committee Chair of Track 6: Displays, Solid-State Lighting, Photovoltaics, and Energy-Efficient Photonics of *Asia Communications and Photonics Conference 2014* (ACP 2014). ACP is the largest and the most influential conference in Asia and Pacific Rim for communications and photonics technologies. ACP 2014, Shanghai International Convention Center, Shanghai, China, November 11–14 (2014)
- International Consultant of technical seminar of the 11th China International Forum on Solid-State Lighting (SSL-China 2014) Guangzhou, China, November 6–8 (2014)
- Member of the International Advisory Committee of the 11th International Symposium on Semiconductor Light Emitting Devices (ISSLED 2017) held in Banff, Canada on October 8–13 (2017)
- Assisting the US Judicial Government Branch (various US District Courts), the USPTO (US Patent and Trademark Office) and the ITC (International Trade Commission) by serving as an independent Technical Expert Witness (1997 to present)

Books

- ***Doping in III-V semiconductors*** (author) Hardback and paperback, 628 pages (Cambridge University Press, Cambridge, UK, 1993). The following excerpt is from a book review by D. L. Miller, *University of Pennsylvania*, University Park PA, which appeared in *Physics Today*, Oct. 1994, p. 71: “[...] Fred Schubert has written a book that very nicely fills two roles: It serves as a reference volume for those of us who use III-V materials, and it provides enlightening explanations of interesting and important problems in semiconductor physics. [...] Schubert, who is employed by AT&T Bell Laboratories, brings his extensive research involvement with III-V materials physics straight to this book. His lucid explanations of some of the important physics of doped semiconductors is a major strength. For example, the chapter on deep centers provides the clearest treatment of the DX center I can remember reading, and it uses the large lattice distortion model and configurational coordinates introduced for the DX center to describe the EL2 deep level. This book can also serve as an excellent reference volume, because it briefly describes epitaxial growth techniques and the doping methods used with them, catalogs dopant-related phenomena, describes characterization techniques and provides 45 pages of citations to published articles and books. [...] I will use it to help my graduate students in the physics of semiconductors. [...] It will certainly be available on my bookshelf, in part to remind me what the Burstein-Moss shift is and in part for the literally hundreds of references that it provides on nearly every topic related to III-V semiconductor doping. Because of its clarity in treating some interesting phenomena of modern semiconductor physics, you too might want to get a copy of this book, even if you believe that Ga and As are just poor alternatives for doping silicon”
- ***Delta doping in semiconductors*** (editor) Hardback and paperback, 616 pages (Cambridge University Press, Cambridge, U. K., 1996)
- ***Light-emitting diodes*** (author) Hardback and paperback, 328 pages (Cambridge University Press, Cambridge, UK, 2003). The following excerpt is from a book review by David Bour, *Agilent Laboratories*, Palo Alto CA, which appeared in *Physics Today*, Nov. 2004, p. 66: “[...] In “*Light-emitting diodes*”, E. Fred Schubert provides an excellent review of the physics and technology of semiconductor LEDs. [...] Interesting anecdotes like [the first demonstration of electroluminescence], clearly written by someone with a broad perspective and expertise, appear throughout the book, making it enjoyable to read. [...] Schubert provides an excellent description of the undesirable [non-radiative] recombination pathway. [...] Schubert has made pioneering contributions to those devices, and this variety of LEDs may become more widely used in the future. [...] Overall, “*Light-emitting diodes*” is an excellent examination of the physics and technology of semiconductor LEDs. The narration is simple and direct, and the book is well referenced for those seeking a deeper understanding of the topic. Written for the graduate level, the text will appeal to a broad audience; and for specialists who make semiconductor LEDs and laser diodes, it will serve as a useful connection to the scientific literature.”
- ***Light-emitting diodes, second edition*** (author) Hardback, 422 pages (Cambridge University Press, Cambridge, UK, 2006)
- ***Physical Foundations of Solid-State Devices*** (author) eBook, 275 pages, ISBN-13: 978-0-9863826-2-8 (Google Books, Mountain View CA, 2015)

- **Light-emitting diodes, 3rd edition** (author) eBook, 672 pages with hundreds of colored illustrations, ISBN: 978-0-9 863826-6-6 (Google Books, Mountain View CA, 2018) “The 1st edition of the book “Light-Emitting Diodes” was published in 2003. The 2nd edition was published in 2006. The current 3rd edition of the book is a substantial expansion of the second edition and has 37 chapters. The book includes a thorough discussion of white light-emitting diodes (LEDs), phosphor materials used in white LEDs, packaging technology, and the various efficiencies and efficacies encountered in the context of LEDs. The background of light, color science, and human vision is provided as well. The fully colored illustrations of the 3rd edition are undoubtedly beneficial given the prominent role of light and color in the field of LEDs. The book is a comprehensive discussion of the LED, particularly its semiconductor physics, electrical, optical, material science, thermal, mechanical, and chemical foundations. The 3rd edition is published in electronic format in order to make the book affordable and easily accessible to a wide readership.”

Courses and laboratories developed at Boston University

- Developed first laboratory for “Physics of semiconductor devices” (SC-471) Fall (1998)
- Developed course “Quantum mechanics applied to semiconductor devices” (SC-574) Fall (1999)
- Developed course “Semiconductor light emitters” (SC-760) Fall (2000)
- Developed distance-learning course and NTU course on “Light-emitting diodes – Device physics and applications” Fall (2000)

Courses taught at Boston University

- Undergraduate Course “Physics of semiconductor devices” (SC-471)
- Graduate course “Fiber optic communication systems” (SC-563)
- Graduate course “Quantum mechanics applied to semiconductor devices” (SC-574)
- Graduate course “Introduction to solid-state physics of devices” (SC-577)
- Graduate course “Quantum electronics” (SC-700)
- Graduate course “Integrated optoelectronics” (SC-770)
- Graduate course “Compound semiconductor devices” (SC-771)
- Graduate course “Light-emitting diodes” (SC-760)
- Graduate course “Research seminar” (SC-860, SC-892)
- Other courses “Research”, “Guided Study”, “Master Thesis”, and “Dissertation” (SC-900)

Courses taught at Rensselaer Polytechnic Institute

- Graduate Course “Semiconductor devices and models II” (ECSE-6290)
- Undergraduate course “Microelectronics technology” (ECSE-2210)
- Undergraduate course “Fields and Waves 1” (ECSE-2100)
- Graduate course “Quantum mechanics applied to semiconductor devices” (ECSE-6968)
- Graduate course “Physical foundations of solid-state devices” (SC-6960)
- Graduate course “Light-emitting diodes and solid-state lighting” (SC-6961)
- Undergraduate course “Introduction to Electronics” (ECSE-2050)
- Other courses “Research”, “Guided Study”, “Master Thesis”, and “Dissertation”

Teaching evaluations and students’ comments

1997 – Students made the following comments: “Clear ... organized ... excellent explanations ... I’ve never had a professor like him – I wish all were like him ... very clear and concise presentations ... strong response to students’ questions and concerns ... Professor provided excellent notes ... laid out lectures in a clear and precise manner which worked out wonderfully ... well organized and confident ... responsive to students’ concerns ... excellent for students going into the semiconductor industry ... excellent hand-outs and course materials ... well prepared ... clear lectures ... I was strongly encouraged ... materials are very interesting ... hand-outs were excellent ... material is very important ... the presentation of materials was very clear ... hand-outs were excellent support to the class ... efforts made by Prof. Schubert in keeping everyone at the same pace was remarkable ...”

1998 – Students made the following comments: “Professor was always well prepared ... excellent content ... very relevant for the field of solid-state devices ... excellent preparation for the class ... handouts were very good ... very well-organized teacher ... excellent knowledge of material ... provided a complete background of all material ... easy to talk to ... excellent overall teaching skills ... really enjoyed coming to class ... his choice of topics and homework helped me a lot ... enthusiastic in teaching and helpful during the office hours ... one of the best professors I have had at BU ... course gave a very good overview of the different solid-state physics principles ... the course was very well organized ... relevant examples and homework were given ... good explanations were

given ... presented clearly ... presentation was clear ... communicated effectively ... very knowledgeable ... good demonstrations in class ... gives clear descriptions ... asks questions of class ... grades homework fairly ... good at answering questions ... no weak points ... excellent instructor and scientist ... inspiring professor ... thorough ... the instructor is very precise and well prepared ... his knowledge of the material is exact ... very responsive to feedback ... encourages student questions, class participation and discussion ... the instructor cared about whether students understood material ... the instructor used applications immediately after showing theory ... handouts were excellent ... guest lecture and lab tour excellent idea ... excellent class notes ... presented topics neatly ... well prepared ... review of ongoing research topics was great ... Professor Schubert is undoubtedly an expert in his area ..."

1999 – Students made the following comments: "He enjoyed teaching the material and was very clear ... the presentation of the material in class was excellent ... he helped me to understand a lot about semiconductors ... Prof. Schubert always tried to make sure that we would all have a clear understanding of the material ... manuscripts were very helpful ... encouraged lots of class participation and was always readily available for help ... presentation was excellent ... the instructor was always willing to help me ... very helpful ... Clearly, Prof. Schubert is *more* than just extremely knowledgeable about this material ... very thorough and exact communication of points ... excellent course packet written by the instructor ... he was very well prepared for class ... He is extremely fair and encourages participation ... he is also very accessible ... excellent instructor ... very approachable and easy to ask questions of ... handouts were very effective and helpful ... Prof. Schubert is very prepared and concepts are well explained ... materials will be very useful for my future ... very open to questions"

2000 – Students made the following comments: "He did a lot of experiments which really helped ... the material is very interesting and cutting edge ... clear presentations ... good in-class demonstrations ... very clear lectures ... the material really does challenge you ... takes the time to answer your questions ... very interesting material ... relevant to today's world of communication ... the field trip was fun ... in-class demonstrations really added to class ... good understanding of course material ... excellent details, willing to help, good explanations ... in-depth details on quantum mechanics ... the instructor was extremely accessible to students ... he encouraged participation in class ... he gave intuitive arguments and explained concepts in a very physical way ... I very much enjoyed Professor Schubert and would like to take more classes with him ... material was very beautiful ... I *very much* enjoyed the papers that were discussed ... everything is well organized ... hand-out material is very complete and clear ... lectures are clear ... the professor prepared an excellent manuscript ... explained things very clearly ... he has strong enthusiasm to solve students' questions ... it's a very important course ... Professor follows the course notes exactly, so one can concentrate on material without having to focus on details ... clearly presented material ... the course is great preparation for future courses in solid-state physics ... I greatly admire Professor Schubert ..."

2001 – Students made the following comments: "He has a thorough understanding of the subject ... I like the fact that he shows us examples in class demonstrations ... the manuscript was good ... instructor provides good notes ... materials are presented clearly ... in this course you learn a lot ... very illustrative and in depth ... very interesting course ... Professor presented the material well ... Professor seemed to have a strong grasp on what he was teaching ... the basics were presented correctly ... smooth transition into more complex materials ... presented basics well ... Professor's strong points are knowledge, organization and class materials ... clear conception ... very important and useful class ... Professor knew what was going on ... manuscript and his notes were very helpful ... responded to suggestions ... notes were comprehensive ... just fine ... manuscript was good ... knows the material very well ... notes handed out are good ... expert knowledge of material ... developed lectures logically and straightforward ... lecture notes were prepared for us - very nice touch ... Professor has deep knowledge of the materials ... Professor is always prepared for lectures ... he emphasizes principles and the concepts ... good preparation ... good stuff and clear presentation ... good research and industry experience ... excellent handout notes and materials ... excellent teaching skills ... inspires the interest of students ... great knowledge of material ... well organized course notes ... Professor Schubert gave very clear instructions ... listening to his presentation is a true enjoyment of an excellent art of lecture style ... the manuscript has the quality of an excellent book ... the manuscript was an excellent reference source book ... the instructor was very clear and well organized and encouraged participation ... text [written by Schubert] was extremely good ... expert knowledge of materials ... class demonstrations were very beneficial ... can clearly relate complex ideas – very good ... has a high amount of patience ... excellent understanding of material ... very enthusiastic in teaching ... always available for discussion ... very knowledgeable ... I don't see any weak points ... he explains the theory very clearly ..."

2002 – Students made the following comments: "Always prepared ... presented difficult material in a manner that was easy to understand ... presented everything neatly ... very helpful and organized ... presents subjects in a very easy and friendly format ... very well qualified ... great experience ... very detailed notes ... well organized ... very useful ... very good diagrams and explanations ... he knows the material extremely well ... notes given to us

are extremely helpful ... professor was very knowledgeable ... was able to answer any of our questions ... very informative course ... very knowledgeable and a great teacher ... the instructor is enthusiastic to teach students ... the instructor can explain the theory very clearly ..."

2003 – Students made the following comments: "Great overall knowledge ... good organization skills ... demonstrations were very interesting and useful ... effective instructor ... handouts were extremely useful and organized ... good course for completely understanding many points of fiber optics ..."

2004 – SPIE short course: "Encouraged questions and handled them well ... excellent short course ... I really appreciated and enjoyed this course ... good course – covered very broad matters ... the instructor was very knowledgeable on the topic ... excellent! ..."; RPI Semiconductor devices and models II (ECSE 6290): Overall excellence of teacher: 4.8 out of 5.0. Student comments: "course was very well prepared ... [course] was very organized ... this is an excellent course ... I learned a lot from this course ... the course was very good ... thanks Prof. Schubert for a wonderful course ... it's been a great course ... thank you ..." RPI Microelectronics Technology (ECSE 2210): Overall excellence of teacher: 4.7 (average 4.2). Overall excellence of course: 4.3 (average 3.9). Student comments: "Understandable presentation ... great job [of] Prof. Schubert ... very nicely done class ... very helpful throughout the entire course ... provided timely explanations to complicated material ... very informative ... course was fun and interesting ... very interesting lecturer ... very down to earth and easy to ask for help ... [instructor] did a good job in presenting [material] ... good course ... fun course ... excellent instructor ... he is a great guy and very knowledgeable ... I would definitely take a class from him again" **Book review** by Neal Oldham (San Jose, CA, USA) on "Doping in III–V semiconductors" (E. F. Schubert, Cambridge University Press, Cambridge UK, 1993) on amazon.com (May 17, 2002): "[This is the] best book I've encountered in the semiconductor field. This is, no question, the best book that I've encountered in the entire field of semiconductor physics. It is expertly organized and indexed, easy to follow, complete in its treatment of electrical and materials-science aspects of III–V semiconductor production and measurement, well-written ... worth every penny if you even have the most remote interest in the subject." **Book review** by Debdeep Jena (Santa Barbara, CA, United States) on "Doping in III–V semiconductors" (E. F. Schubert, Cambridge University Press, Cambridge UK, 1993) on amazon.com (July 6, 2001): "Very useful text for semiconductor crystal growers. Doping is a big, big issue in semiconductors; this text does appreciable justice in its treatment of the issue. In addition, Schubert treats heterostructure physics appreciably well (in fact better than many textbooks on semiconductor physics!). Perusal of this book has proved very rewarding for me, and I expect it will do the same wonder for you too."

2005 – SPIE Photonics West short course student comments: "Very good instructor! ... very knowledgeable ... clear on complex subjects ... good job fielding questions ... (numerical score 4.3 out of 5.0). Educational materials on the web: ... I have greatly enjoyed your LED slideshow. CLEO short course: ... very good and well-organized course!" ECSE 6968: "Class presentations were very helpful in learning ... very useful in learning *the details* of fundamental concepts ... the course is very good ... the course is excellent for engineers ... your [...] treatment brought about a much better understanding ... examples were great and helpful ... [discussion of] history and photons [...] helped increase interest ... After your course now, I can actually approach a quantum mechanics text book without fear ... overall, I just wanted to say – *thank you* ... excellent course ... the instructor made it interesting and taught very effectively ... the manuscript provided was also very well written ... class was excellently structured ... will benefit my studies in the future ... especially liked the term paper requirement ... Prof. Schubert is an excellent instructor, who is well prepared ..." (excellence of instructor: 4.8 out of 5.0). SPIE Photonics North short course: "Very good and clear in presentation ..." (numerical score 4.4 out of 5.0). ECSE 6960 mid-course and final feedback by students: "Professor has provided all course materials ... I really appreciate it ... well presented ... technical support was great ... my learning experience has been good ... responses to my homework questions have been very timely ... I have enjoyed the course and found it interesting and useful ... homework assignments have been extremely beneficial ... the set of notes is very comprehensive ... good class structure ..." (numerical scores of students' course and instructor evaluation: 5.0 out of 5.0). Comment on web educational materials: "Notes look very thorough and clear ..."

2006 – SPIE Photonics West short course student feedback: "Excellent, knowledgeable ... excellent presentation ..." (numerical score 3.91 out of 5.0). ECSE 6961 (Light-emitting diodes and solid-state lighting): "excellent ... Informative, comprehensive and interesting ... the best part of this course, in terms of my learning experience, has been the course materials ... just an outstanding class ... so much is newly discovered and so much is current on-going research and commercially relevant ... Dr. Schubert is obviously a leading researcher and did a great job of conveying his experience and understanding to the class ... a highly technical topic that still makes a good general conversational topic ... I liked the course material ... I liked the fact that Prof. Schubert lectured directly from the textbook ... I liked the structure of the course ... I learned a lot about lasers and LEDs and other optical devices ... it is a basic and fundamental class ... the instructor gives ideas, concepts, and samples very clearly ... very good course ... students interested in LEDs and solid-state lighting are strongly recommended to take it ... liked the overall coverage ... the teaching pace was good ... he covered a lot of material that is

important for the subject, but it was clearly always related to the topic ... the manuscript that he let us use was excellent in my opinion ... the most important thing I liked about the course was the course material and the structure of the course ... right amount of homework and the two exams and the term paper presentation ... it was great to learn this course from someone who is a world leader in this field ... well-organized material ... liked the course format ... organization was good ... allowed me to know exactly what we were covering so I could look through the material prior to the lecture ... course content was good, starting with LED basics and covering materials through modern technologies, and then a look at solid-state lighting and sort of an intro to communication devices ... good fundamentals in LEDs ... GREAT Professor ... awesome course ... informative course ... ability to view course materials online was helpful ... very fruitful course ... covering a lot of materials ... very good and very important for graduate students to take this one ... for people in industry it's also useful ... for the instructor, this course is thought through very clearly ... the text book is also very good ... great course ... excellent instructor ... cute instructor ... course is very good ... I benefited a lot from it ..." (numerical scores: 4.7 out of 5.0). ECSE 2210 (Microelectronics Technology) student comments "Excellent teaching method ... I like that the Professor asks random questions at the end of class – it helped me understand the subject better ... I thought Prof. Schubert was fabulous ... his organization of the class encouraged learning ... I highly recommend this class to everyone ... a devoted and involved teacher ... displayed more enthusiasm in teaching than other Professors I had ... he also seemed to have a philosophy about teaching that was beyond helping students get good grades ... he emphasized real-world applications of material and had general advice about working in the real world after leaving academia ... helpful ... although he was harder in grading and exams, Prof. Schubert challenged us more and made the course more interesting ... the many class activities provide lots of practice of materials just learned ... provided good back-up information ... made sure students understand concepts ... thank you for asking students questions during class to reinforce concepts ... thank you for allowing open book exams ..." (numerical scores: excellence of teacher 4.4 out of 5.0; excellence of course 4.3 out of 5.0; overall average of ratings 4.4 out of 5.0)

2007 – Book review by Steven J. Wojtczuk (Lexington, MA, USA) on "Light-Emitting Diodes" (E.F. Schubert, Cambridge University Press, Cambridge UK, 2003) on amazon.com (March 14, 2006): "Schubert (RPI) has written an excellent book on LEDs that manages to explain and derive simple quantitative models for many phenomena of current interest ... many monographs are a compendium of results in the field with hundreds of references ... in contrast, Schubert, while giving copious references, is the sole author, leading to a coherent presentation well suited to learning ... there are plentiful and good figures and drawings, as well as many exercises and solutions integrated into the text ..." SPIE photonics West Short Course: "Excellent talk ..." ECSE 2210 (Microelectronics Technology) "Thank you ... great course ... excellent instructor ... interesting course ... appreciated that you did not lecture completely from the slides and that you probed the class to ensure that we were understanding the key points ... course is fine ... good professor ... Professor Schubert is one of the best lecturers I had ... the pace at which he moves the topic, the way he explains things, and the manner in which he asks students questions all came together to help me learn much more from his lectures than I could on my own ... instructors are absolutely very intelligent ... Professor Schubert was a good professor ... I actually learned things when Professor Schubert taught ..." ECSE 6968 (Physical Foundations of Solid-State Devices) "The instructor explained every concept in a very simple and effective manner ... I really enjoyed taking this course ..." (numerical scores: 4.5 out of 5.0)

2008 – SPIE Photonics West short course feedback: "Very good ... clear ... very nice ... answered questions readily ..." (numerical score 4.3 out of 5.0) ... ECSE 6961 (Light-emitting diodes and solid-state lighting) feedback: "It was great for me to have the opportunities to take two consecutive classes, *Physical Foundation* and *LEDs*, from you ... both these classes have taught me a lot ... they were very well organized ... thank you for all the help ... I have really enjoyed your classes ... relevant material ... very good professor ..." (numerical scores: 4.3 out of 5.0) ... Internet educational materials feedback: "I recently came across your course notes while trying to get a basic understanding about semiconductors and I wanted to thank you. Your notes for course "ECSE-2210 Microelectronics Technology" are the most useful and informative thing I have found on semiconductors on the Internet. I'm a chemist by trade and this is a great introduction for me ..." 2007 Chautauqua Short Course and High School Teacher Summer Course, held at RPI June 26 and July 12, 2007 (numerical average of scores: 9 out of 10) ... ECSE 6968 (Physical Foundations of Solid-State Devices) feedback: "Prof. Schubert is one of the best professors I've ever had ... his ability to explain difficult and complex materials in a clear and concise manner is unmatched ... the presentations, although time consuming, I felt were a great idea ... thanks for your efforts professor! ... I have really enjoyed taking this course ..." By email: "Thank you professor ... it has been a pleasure taking this course with you ..." (numerical scores: 4.4 out of 5.0)

2009 – SPIE Photonics West short course feedback by students: "One of the best short courses I have taken ... it was very nice to hear about the history of LEDs ... very interesting but also very theoretical ..." (numerical score 4.1 out of 5.0). ECSE 2210 (Microelectronics Technology) "Great course ... instructors were excellent ... encourages students to stay up to date with the subject matter ... Thanks for this well-organized class ... [the instructor] tries

to get students to come out with the best grade possible ... this was a good class ...” ECSE 6968 (Physical Foundations of Solid-State Devices) feedback by students: “It is really an excellent course ... clear hand script ... great professor! ...” (numerical scores: 4.7 out of 5.0)

2010 – SPIE Photonics West short course feedback by students: “Good to get the latest data and charts ... very good ... very broad course and well organized ... it was great ...” (numerical score 4.04 out of 5.0) ... ECSE 6961 (Light-emitting diodes and solid-state lighting) feedback by students: “A good course ... this was a wonderful course ... it has given me a lot of understanding ... the course has inspired me to take up LED research ... useful ... straight forward ... very good advisor ... good course ...” (numerical scores: 4.3 out of 5.0) ... ECSE 6220 (Physical Foundations of Solid-State Devices) feedback by students: “Overall excellent course ... Professor Schubert is a good teacher ... he can explain every discipline very clearly and relate them to practical applications ... I like his teaching style very much ... overall, it was a nice course ... material explained in a clear organized manner ...” (numerical scores: 4.7 out of 5.0)

2011 – SPIE Photonics West short course feedback: “Very nice overview ... the instructor was excellent! ... very good instructor ... I would recommend lengthening to 6 hours ... excellent presentation, materials and text ... thanks ... very clear and easy to follow ... to be recommended ... excellent presentation ... good compromise for a person with a busy schedule ...” (numerical score 4.45 out of 5.0); ... ECSE 2210 (Microelectronics Technology) “This was a great course ... I enjoyed Professor Schubert’s views ... I was successful ... this course was taught very well ... this subject I now find quite interesting and am no longer intimidated by it ... I liked the material of this course ... thank you ...” (numerical scores: 3.3 out of 5.0); Feedback on book *Light-Emitting Diodes*: “I am a graduate student from National Chiao Tung University, Taiwan ... your wonderful book *Light-Emitting Diodes*, both first- and second-edition, gave me a lot of information and help ... I would like to ask when can the third of the masterpiece be published? I wish I can get it as soon as possible and study more about the lighting devices; Feedback on Internet pages: I found your website and information [...] quite enlightening and provides a great start ... I simply wish to quickly express my thanks and gratitude.” Feedback on book *Physical Foundations of Solid-State Devices*: “Dear Prof. Schubert, I have read your book *Physical Foundations of Solid-State Devices* and I must say it is amazing the explanations are really good and I am most thankful that you have decided to put the book online thank you.” Itamar Jade Balla, The Israel Institute Of Technology. Feedback on book *Light-Emitting Diodes* by Trung Nguyen (San Jose, California): “It is a good book about Light Emitting Diodes (LEDs). It provides very good info and it is a good reference for engineers who work in the LED field”; ... ECSE 6220 (Physical Foundations of Solid-State Devices) feedback: “Amazing course ... great instructor ... very good course ... The text and lectures were very useful and informative ... I definitely learned a lot from taking this course ... I liked the course materials! ...” (numerical scores: 4.6 out of 5.0)

2012 – Feedback on Internet-based materials: “I’m Cheng Liu [Wuhan National Laboratory for Optoelectronics, China], currently a graduate student majoring in Physical Electronics ... I deeply admire your profound knowledge on this field and your unselfish sharing of it ...”; ... SPIE Photonics West short course feedback: “Dr. Schubert was very clear and very patient with people who had questions ... the materials were comprehensive ...”; Feedback on Internet-based materials: “Supremely-rich course contents posted on your website. Thank you very much for showing such awesome materials for the world to see ...” (Prof. Natee Tangtrakarn, Thailand) ... ECSE 6962 (Light-Emitting Diodes and Solid-State Lighting) feedback: “... very interesting course ... Professor Schubert did a great job explaining the material ... his textbook is very clear and understandable ... nice course ... I learned a lot of new things by taking it ...” (numerical scores: 4.7 out of 5.0)

2013 – *SPIE Photonics West short course* feedback (SC-052, Light-Emitting Diodes): “Great instructor with admirable combination of knowledge in academic and commercial knowledge ... I appreciated the depth of his knowledge and experience ... the length of the course was good ... Overall this was an excellent course ... Thank you ... course is very easy and I understand it easily ... Excellent course! ... Instructor was fantastic -- clear, explicit, took questions as we went and answered well ... One of the best SPIE courses I've taken (and I've taken lots)! ... Great course -- thanks! ... I was happy that the slides were updated with 2012 data”. **RPI course numerical scores (ECSE-6962, Light-Emitting Diodes and Solid-State Lighting)**: Numerical score of students’ evaluations: 4.67 out of 5.0; Verbatim comments: “The course is pretty good ... needs no improvement ... I can appreciate the more wide-angle approach from the course ... These areas are very important and previously I had no knowledge of them ... It was a pleasure attending your class ...” **RPI course numerical scores (ECSE-6968, Physical Foundations of Solid-State Devices)**; Verbatim comments: “It has been an awesome experience of learning for me in this course ... Thank you for everything ... Thank you for the great semester ... Have a good break ... Thank you for the great semester ... Have a good break ... Professor, thank you for an engaging and interesting class this semester ... I enjoyed the subject of my paper and learned quite a bit particularly about GaN, which I had not had a chance to really do any research into before ... Very good and interactive class ... I liked the style of the class ... I thought the topics covered were very interesting ... I think I got much more out of the class this way than if we would have followed the manuscript chapter by chapter ...” Numerical score of students’ evaluations: 4.83 out of 5.0

2014 – SPIE Photonics West short course verbatim feedback (SC-052, Light-Emitting Diodes): “Very knowledgeable instructor ... the course was packed with information ... handouts are excellent ... Excellent presentation and contents ... the color rendering section which was interesting and fun ...” Numerical score of students’ evaluations: 4.36 out of 5.0; **RPI Course ECSE-2210 Microelectronics Technology**; Verbatim comments: “Instructor is clearly very knowledgeable about the topics ... Very clear and comprehensive ... This is the best class ever ... I'm quite enjoying this course ... I don't really have any recommendations on things to change ... The homework and lectures being sent out at the beginning was very helpful ... Both the TA and the professor were able to explain things very well ... I think he is a good lecturer ... I think the homework each was very, very good at teaching me the material, and the exam was fairly graded and easy to understand ... I definitely like the professor and I would have him again ... A good class ... I enjoyed Prof. Schubert's style of teaching ... I would still recommend Prof. Schubert as a professor ... Microelectronics is a good class ... Prof. Schubert keeps it interesting though ... he's a great professor ... The two TAs are also great ...” Numerical score of students’ evaluations of instructor: 4.25 out of 5.0. **RPI Course ECSE-6220 Physical Foundations of Solid-State Devices**; Verbatim comments: “The book and lectures seem to be entirely in sync with one another ... it really enforces the material covered in the book ... the material is covered thoroughly and improves students' understanding of quantum physics ... The class was interesting with excellent learning materials ... I loved how the course was so well organized ... The lectures were very well put together ...” Numerical score of students’ evaluations of instructor: 4.75 out of 5.0.

2015 – SPIE Photonics West Short Course SC-052 titled Light Emitting Diodes, Verbatim comments: “I was very satisfied with this short course” Numerical score of students’ evaluations: 4.53 out of 5.0; **RPI Course ECSE-6960 Light-Emitting Diodes**; Verbatim comments: “the class has been excellent! ... I've learned a good amount about LEDs ... Also I'd like to thank you for a great semester and say that you've peaked my interest in the LED field! ... I would like to add that the course was an excellent experience for me and that I really enjoyed learning about LED technology! ... Thank you very much for teaching such a wonderful class ... It was a great learning course” Numerical score of students’ evaluations: 5.0 out of 5.0. **RPI Course ECSE-2100 Fields and Waves 1**; Verbatim comments: “This class is going perfectly and I love the way it's run ... The material is great and understandable ... the pace is perfect ... I like the pacing of the course and the fact that we spend time really developing an understanding of the theory and concepts that we will be using ... I like the Professor ... The lectures are great ... I really enjoy this professor and he is very understanding of the students’ levels of learning and focused on that ... Professor Schubert is clear and easy to understand ... Overall a very good professor ... very knowledgeable and helpful ... I thought the professor was very knowledgeable and was an excellent instructor ...” Numerical score of students’ evaluations of instructor: 4.17 out of 5.0.

2016 – SPIE Photonics West Short Course SC-052 titled Light Emitting Diodes, Verbatim comments: “This has been my favorite course (over 3 years) ... Well-structured presentation, and well given ... I was surprised by how much I didn't know. I learned a lot ... Explained difficult concepts in a clear and simple manner ... Able to go "off script" to clarify during questions.” Numerical score of students’ evaluations: 4.56 out of 5.0; **RPI Course ECSE-2100 Fields and Waves 1**; Verbatim comments: “This is cool material ... This class was one of the most well put together I have ever taken in terms of lecture pace, lecture clarity, TA support, and quality of teaching and communication ... The lectures never felt too long or too short, the pace was good, I never felt lost or without an option to turn for help ... The homework was neither too long nor too short, and was well balanced with conceptual and quantitative questions ... Prof. Schubert's lecture style was very clear, concise, and to the point, with many useful examples in real life scenarios which made the material more interesting ... Very well done ... Great class ... I liked the pace of the class ... it helps with understanding the material a lot ... The labs [...] were fun and very educational ... Overall, I learned a lot from this course ... The speed of the class is perfect ... I really got a chance to learn ... This professor is very good ... Also, [in] the lab section I was able to really break down what I learned in class ... Schubert has the neatest handwriting of any professor I've ever had in my 3 years here ... His diagrams are extremely neat and he is easy to understand verbally too ... Lots of conceptual knowledge covered ... Overall [...] it was an enjoyable class ...” Numerical score of students’ evaluations: 5.0 out of 5.0. **RPI Course ECSE-2210 Microelectronics Technology**; Verbatim comments: “So far, this has been one of my favorite courses at RPI ... I'm a huge fan of Prof. Schubert's ability to clearly describe concepts both conceptually and mathematically ... Class activities [...] were really helpful! ... Otherwise the class is great! ... Prof Schubert knows his stuff ... Best professor I have had ... This course was well taught ... Professor Schubert's explanations were very clear and understandable ... he took time to address student questions with in-depth answers ... I feel as though I gained a lot from this course, especially with regards to explanations of why certain things in ECSE-2050 (Intro to Electronics) occur the way they do like where the diode property comes from and how material properties of electronic components give rise to the very real circuit characteristics we see in ECSE-2050 labs ... In this sense, Microelectronics Tech is a very good companion class to Intro to Electronics, and I highly recommend future students take them at the same time ... this was a quite good class ... Best MET instructor ... I was so actively engaged during the lectures that it was kind of scary ... The lecture notes and lectures were mostly great ... The material covered in it was succinct and interesting,

yet still covered the knowledge needed to tackle engineering problems in semiconductors ...” Numerical score of students’ evaluations: 4.64 out of 5.0.

2017 – RPI Course ECSE-2100 Fields and Waves 1; Verbatim comments: “I thoroughly enjoy this class ... Schubert is awesome! ... Enjoyed the class ... He is a good teacher ... Most teachers talk really fast making it hard to follow ... Schubert talks slow and explains things really well ... Professor Schubert is an excellent professor, and has been one of my favorites at RPI so far ... He made a difficult topic approachable, interesting and understandable ... I hope I have him as a professor in the future ... Thank you ... I enjoyed this class, especially the labs ... Lectures were good too ... great class! ... The professor does a great job of engaging the students by asking questions and making students ask questions to make them think about the labs ... This course is overall excellent in that the professor does know the pace of class and gives feedback appropriately ...”; Numerical score of students’ evaluations: 4.63 out of 5.0. **SPIE Photonics West Short Course SC-052 titled Light Emitting Diodes,** Verbatim comments: “the course covered a wide variety of concepts ...” Numerical score of students’ evaluations: 4.03 out of 5.0.

2018 – RPI Course ECSE-2100 Fields and Waves 1; Verbatim comments: “Professor Schubert is great and very entertaining to listen to in the lab and in lecture ... Really appreciate how Prof. Schubert structures lectures ... Schubert is great! ... The professor is excellent at relaying concepts ... This course is very interesting and it goes at a good pace ... One of the better professors here at RPI ... He cares about his students and helps them to learn the most through lectures and labs ... Fantastic course that goes into great detail into not only knowing the material but also understanding the material ... [the course] has been clarified and allowed for a greater learning process.” Numerical score of students’ evaluations of instructor: 4.17 out of 5.0. **RPI Course ECSE-6220 Physical Foundations of Solid-State Devices;** Verbatim comments: “Perfect professor, no complaints.” Numerical score of students’ evaluations (median): 5.0 out of 5.0.

2019 – RPI Course ECSE-2100 Fields and Waves 1; Verbatim comments by students: “Schubert is excellent in relating information in a practical manner especially in the lab ... Overall, both the professor and TAs prioritize if students understand material over semantics in reports and homework, which is really helping me in the course, and feedback given is incredibly helpful in both ... Schubert is a mystery. He speaks very slowly and clearly, but you somehow learn everything at a very fast rate ... Class [...] being just the right amount focused and adequately paced ... Overall great class ... Labs were educational and we were allowed to have fun with it ... Otherwise great lectures, notes were available and understandable ... this was one of my favorite classes ... Very well run by Schubert ... lectures were informative and easy ... labs were fun ... The TA's were allowed to have personalities and interact with the students ... 10/10 would take again ... Schubert was okay ... The best parts about the course for me were everything was online and I could copy the notes at my leisure with my busy schedule ... I also liked that exams were open book and we had a lot of opportunities for practice ... I have nothing but good things to say about both TAs and Professor Schubert – this has been my favorite class this semester ... Though challenging, I have found the course material very interesting and all teachers have been excellent ... Course was good ... I like Professor Schubert's class notes online. They're super well written and helpful.” Numerical score of students’ evaluations of instructor: 4.63 out of 5.0 (average) and 5.0 out of 5.0 (median).

2019 – RPI Course ECSE-6280 Light Emitting Diodes; Verbatim comments by students: “This was a great course ... I learned a lot during the semester ... Great class ... I really enjoyed Professor Schubert's expertise on the subject ... Gives both in-depth technical knowledge as well as high level background to better understand the driving factors of the LED industry ... I would highly recommend it to anyone in ECSE.” Numerical score of students’ evaluations: 4.83 out of 5.0 (average) 5.0 out of 5.0 (median).

2020 – RPI Course ECSE-2100 Fields and Waves 1; Verbatim comments by students: “I really enjoyed this class ... the cool labs with good help and good lectures made me really enjoy this class and help the information stick in my head better ... The labs provided a great use to show theory in practice and how certain concepts are applied to real-life applications ... The laboratory session was also a great time to ask questions and have in-depth talks about the material ... I would have already commended this professor for class organization and material availability prior to online courses (course material easily available, organized well, and easy to understand; interactive lectures; interactive labs better than most other ECSE courses), Prof. Schubert handled the change to online coursework best of all of my professors and maintained the quality of lecture almost perfectly ... The 'live' online classes were interactive and courteous by students and the professor, organized, and just as in-depth as before, even including miniature homemade demonstrations and experiments ... The course was taught very fundamentally which allowed me to think and learn more ... Thank you, Professor Schubert ... I really missed your live lectures and labs! ... Professor Schubert made the best of the situation of online learning ... Great class ... I learn a lot from this class ... I enjoy lab sessions and try never to miss any class ... Prof. Schubert is really good!” Numerical score of students’ evaluations: 4.75 out of 5.0 (average) 5.0 out of 5.0 (median).

2020 – RPI Course ECSE-2050 Introduction to Electronics; Verbatim comments by students: “I really enjoyed how easy it was to follow along with the lecture ... I really enjoyed the content of this course, and I feel that the

applications of this content in the lab were extremely effective to help students understand the content ... the concepts in general were extremely interesting ... I liked how the lecture sessions for this class provided much more room for discussion and examples than nearly any other ECSE course I have taken at RPI so far ... Schubert was very aware of the students ability to fully comprehend the topic ... He was very patient with the students that needed extra explaining ... I learned a lot about the course material ... I liked the one-on-one attention we received in the in-person lab ... I enjoyed the in person laboratory sessions, they were a good place to get all my questions answered ... I really like the lecture notes and the detailed diagrams / graphs that help explain the concepts ... Professor Schubert does a great job of breaking down the material, he always tries to engage the students in every lecture ... Very clear notes, responded quickly, answered any confusing questions really well, and very nice and accommodating towards the current COVID situation everyone is going through ... He had very organized notes that helped especially with the difficulties of online learning ... I loved the explanation of diodes, it's never been so clear to me before! ... Examples were excellent ... The course was great! ... I learned a lot and this course stimulated my interest ... Very engaging ... stimulates participation ... Professor Schubert was a refreshing exception ... the professor was very knowledgeable in the subject area ... explanations were clear and easy to understand ... I really like the format of this class compared to my other classes ... I really enjoyed the format ... Very detailed lecture, very helpful with students, made very complex material easy to understand ... Prof is really understanding and cares about his students ... He is really willing to work with us which I found is really rare at RPI ... He is easily one of the best professors I have had ... He cares most about whether we are learning and understanding, rather than following his desired schedule perfectly ... Cannot say anything bad about Prof Schubert ... Class is great" Overall instructor rating: 4 out of 5. Overall course rating: 4 out of 5.

2021 – RPI Course ECSE-2050 Introduction to Electronics; Verbatim comments by students: "Class has been going smoothly ... Professor Schubert includes real world-examples of devices in his lectures, showing the importance of our course materials ... He is always very considerate of students, trying to adapt to what would help people most ... He engages students in lectures." Overall instructor rating: 4.8 out of 5.0. Overall course rating: 4.6 out of 5.0.

2021 – RPI Course ECSE-2050 Introduction to Electronics; Verbatim comments by students: "Professor is always able to conceptually answer our questions, and run through circuit analysis with us if the results we're measuring don't match up ... I tried taking this class once before, and I failed it. This time around, I feel like I know everything about everything. I had never imagined just what a difference teaching style could make in my ability to learn information, but this class is so much more welcoming to me this time around. It was with a different professor the first time. I much prefer Professor Schubert and the way he conveys information so effortlessly. He also seems like he's passionate about teaching the information and his handwritten notes are astonishingly detailed ... Great professor! I appreciate Professor Schubert taking the time to clarify different topics and always checking in with the students. He seems to genuinely care about our education. He is strict about deadlines, more so than other professors at least, but I think he has earned that ... Professor Schubert is very friendly to his students ... He was very helpful and one of the few professors who actually stays and talks to students all throughout the lab period. It was very helpful because often I would think that I fully understood a concept and then he would ask a question that would either stump me or reinforce information. Additionally he kept lectures short and to-the-point, which I appreciate." Overall instructor rating: 4.3 out of 5.0. Overall course rating: 4.3 out of 5.0.

2022 – RPI Course ECSE-2050 Introduction to Electronics; Verbatim comments by students: "Great professor! ... Handwriting is amazing ... His notes are flawless and easy to understand ... This course covers much more than most other EE courses I've taken, and yet I feel as though this has been the easiest EE course due to his teaching abilities ... Professor Schubert is a very knowledgeable professor ... It's clear that he wants his students to learn ..." Overall instructor rating: 4.3 out of 5.0. Overall course rating: 4.4 out of 5.0.

2022 – RPI Course ECSE-2210 Microelectronics Technology; Verbatim comments by students: "I think Schubert does a great job of teaching ... He makes the pn junctions as interesting as he can ... I also love the chalk-board! So great, every professor should be forced to use it, because you can follow the work so smoothly (not like powerpoints) ... I would not change the class ... I also like how Prof. Schubert asks for feedback from everyone after class ... Course was at a great pace and the level of difficulty ... Professor Fred Schubert is one of my most favorite professors at RPI ... I am sad to see in the course schedule for Spring 2023 that he is not teaching any 4000 level ECSE courses ... I think that the department and students are missing out by not having someone as knowledgeable as him teaching more conceptually hard topics because Professor Schubert does that exceptionally ... Best ever lecture experience, clear structure of lecture notes, comprehensive homework that helps to improve students' understandings, and always eager to solve students' questions ... Thanks for another great course Professor!"

2024 – RPI Course ECSE-2050 Introduction to Electronics; Verbatim comments by students: "... It's great to learn how a component works and learn "Iconic Circuits" that use those components ... I really appreciated the

Homeworks, they were well thought out and helped me understand the content ... I liked the open notes exams, they allowed me to use the notes I took in class and demonstrate how I can apply the concepts we learned in class to a different problem ... I appreciated [Professor Schubert] talking to everyone in [the] lab one-on-one ... I also liked that he showed interest in all the students and answered our questions promptly and thoroughly ... Very nice and understanding professor, one of the best in the ECSE department ... Professor Schubert seems to know what he is talking about ... Professor Schubert is very nice and during labs walks around and asks students questions making sure we understand the concepts ... He also introduced some applications not taught in the previous versions of the course and even added a lecture on class-D amplifiers to attempt to keep the course up with modern technology ... The last few lectures left a good impression though and were extremely engaging ...”

2024 – RPI Course ECSE-2210 Microelectronics Technology; Verbatim comments by students: “... Professor Schubert is very passionate about his subject and that passion rubs off on his students ... The professor was truly excellent and I enjoyed attending his lectures twice a week ... He was very good at teaching. ...”

2025 – RPI Course ECSE-2050 Introduction to Electronics; Verbatim comments by students: “... having the notes on a shared drive was extremely useful for me for keeping up ... Best professor I've had by a long shot ... Amazing Professor, I really enjoyed the class and his commitment to students, especially in the lab ... The class was interesting, well-paced, and greatly improved my understanding of circuitry on a theoretical level ... This course was fairly good ... the content was fine ... ”

Post-doctoral & visiting personnel for which I served as Major Research Advisor

Dr. Li-Wei Tu	Post-Doctoral Fellow	1988–1990
Dr. Neil Hunt	Post-Doctoral Fellow	1991–1993
Dr. Matthias Passlack	Post-Doctoral Fellow	1993–1995
Dr. Wolf Grieshaber	Post-Doctoral Fellow	1995–1997
Dr. Thomas Gessmann	Post-Doctoral Fellow	2000–2002
Dr. Jong Kyu Kim	Post-Doctoral Fellow	2003–2005
Dr. Min Ho Kim, SEMCo	Visiting Engineer	2007–2008
Prof. Ji-Myon Lee, Sunchon Univ.	Visiting Professor	2007–2008
Dr. Jaehee Cho	Post-Doctoral Fellow	2008–2009
Dr. Yongjo Park, Samsung LED	Visiting Vice President	2010–2012
Dr. Yangang Andrew Xi	Visiting Scientist	2013–2014
Dr. Guan-Bo Lin	Post-Doctoral Fellow	2014–2015

Graduate students for which I served as Major Research Advisor

Dr. Dean A. Stocker	Ph.D. Dissertation	Ph. D. completed in 1999
Xiaoyun (Jane) Guo	Master Thesis	M.S.E.E. completed in 1999
John W. Graff	Master Thesis	M.S.E.E. completed in 1999
Dr. Ian D. Goepfert	Ph.D. Dissertation	Ph. D. completed in 2000
Yun-Li Li	Master Thesis	M.S.E.E. completed in 2000
Dr. Xiaoyun (Jane) Guo	Ph.D. Dissertation	Ph. D. completed in 2001
Dr. John W. Graff	Ph.D. Dissertation	Ph. D. completed in 2002
Dr. Erik L. Waldron	Ph.D. Dissertation	Ph. D. completed in 2002
Jay M. Shah	Master Thesis	M.S.E.E. completed in 2002
Dr. Yun-Li Li	Ph.D. Dissertation	Ph. D. completed in 2003
Jingqun (“JQ”) Xi	Master Thesis	M.S. completed in 2003
Yangang Andrew Xi	Master Thesis	M.S. completed in 2003
Ronald Jackson	Master Thesis	M.S. completed in 2004
Sameer Chhajed	Master Thesis	M.S. completed in 2004
Hong Luo	Master Thesis	M.S. completed in 2005
Xiaolu Li	Master Thesis	M.S. completed in 2005
Kaixuan Chen	Master Thesis	M.S. completed in 2005
Dr. Jay M. Shah	Ph.D. Dissertation	Ph. D. completed in 2006
Frank Mont	Master Thesis	M.S.E.E. completed in 2006
Dr. Hong Luo	Ph.D. Dissertation	Ph. D. completed in 2006

Dr. Jingqun ("JQ") Xi	Ph.D. Dissertation	Ph. D. completed in 2006
Dr. Yangang Andrew Xi	Ph.D. Dissertation	Ph. D. completed in 2006
Won Seok Lee	Master Thesis	M.S. completed in 2007
Qi Dai	Master Thesis	M.S. completed in 2007
Di Zhu	Master Thesis	M.S. completed in 2007
Jiuru Xu	Master Thesis	M.S. completed in 2007
Ahmed Noemaun	Master Thesis	M.S. completed in 2007
Roya Mirhosseini	Master Thesis	M.S. completed in 2008
David Poxson	Master Thesis	M.S. completed in 2008
Qifeng Shan	Master Thesis	M.S. completed in 2009
Ming Ma	Master Thesis	M.S. completed in 2010
Xing Yan	Master Thesis	M.S. completed in 2010
Dr. Roya Mirhosseini	Ph.D. Dissertation	Ph. D. completed in 2010
Dr. Sameer Chhajer	Ph.D. Dissertation	Ph. D. completed in 2010
Dr. Jiuru Xu	Ph.D. Dissertation	Ph. D. completed in 2011
Dr. Frank Mont	Ph.D. Dissertation	Ph. D. completed in 2011
Dr. Wonseok Lee	Ph.D. Dissertation	Ph. D. completed in 2011
Dr. Di Zhu	Ph.D. Dissertation	Ph. D. completed in 2011
Dr. Qi Dai	Ph.D. Dissertation	Ph. D. completed in 2011
Dr. Ahmed Noemaun	Ph.D. Dissertation	Ph. D. completed in 2011
Dr. David Poxson	Ph.D. Dissertation	Ph. D. completed in 2011
Dr. Qifeng Shan	Ph.D. Dissertation	Ph. D. completed in 2012
Dr. Ann Mao	Ph.D. Dissertation	Ph. D. completed in 2013
Dr. Xing Yan	Ph.D. Dissertation	Ph. D. completed in 2013
Dr. Ming Ma	Ph.D. Dissertation	Ph. D. completed in 2013
Dr. David Meynard	Ph.D. Dissertation	Ph. D. completed in 2013
Dr. Guan-Bo Lin	Ph.D. Dissertation	Ph. D. completed in 2013

Expert Witness Consulting Service

- 1997** **Case:** Hewlett-Packard Company versus CEO of United Epitaxy Company (Taiwan)
Nature: Trade secret misappropriation
Venue: U.S. District Court.
Law firm: Morrison & Foerster LLP, Washington DC.
Role: I served as technical expert witness on behalf of United Epitaxy (Defendant). I wrote one or more expert reports.
- 1998** **Case:** Hewlett-Packard Company versus United Epitaxy Company (Taiwan)
Nature: Patent infringement.
Venue: U.S. District Court for the Northern District of California.
Law firm: Quinn Emanuel Urquhart Oliver and Hedges LLP
Role: I served as technical expert witness on behalf of United Epitaxy (Defendant). I wrote one or more expert reports.
- 2006** **Case:** Kerr Company versus 3M and Dentsply International Company.
Nature: Patent infringement.
Venue: U.S. District Court for the Western District of Wisconsin.
Law Firm: Woodcock Washburn LLP, Philadelphia, Pennsylvania.
Role: I served as technical expert witness on behalf of Dentsply (Defendant). I wrote one or more expert reports.
- 2006** **Case:** Nichia Corporation (Japan) versus Seoul Semiconductor Company (Korea).
Nature: Design patent infringement.
Venue: U.S. District Court for Northern District of California, San Francisco Division.
Law firm: Foley & Lardner LLP Washington DC.
Role: I served as technical expert witness on behalf of Nichia (Plaintiff). I wrote one or more expert reports; I was deposed.
- 2008** **Case:** Seoul Semiconductor (SSC) Company LTD (Korea) versus Nichia Corporation (Japan).
Nature: Patent infringement.
Venue: U.S. District Court for the Eastern District of Texas, Beaumont Division.
Law firm: Morrison & Foerster LLP, Palo Alto, California.
Role: I served as technical expert witness on behalf of Nichia (Defendant). I wrote one or more expert reports; I testified in District Court during the claim construction / Markman hearing.
- 2008** **Case:** Professor Gertrude Rothschild versus Toshiba Company (Japan).
Nature: Patent infringement.
Venue: U.S. International Trade Commission (ITC), Washington DC.
Law firm: DLA Piper LLP, San Francisco California.
Role: I served as technical expert witness on behalf of Toshiba (Defendant). I wrote one or more expert reports; I was deposed.
- 2008** **Case:** Honeywell Company versus Cree Company and Lumileds Company.
Nature: Patent infringement and Reexamination of patent.
Venue: U.S. District Court for the Eastern District of Texas, Marshall Division. Reexamination before the USPTO's Patent Trial and Appeal Board.
Law firms: Paul Hastings LLP, Washington DC and Ingrassia, Fisher & Lorenz PC, Washington DC.
Role: I served as technical expert witness on behalf of Honeywell (Plaintiff). I wrote one or more expert reports. I testified at the USPTO during a re-examination hearing.

- 2010** *Case:* Landmark Screens Company versus MLB Company and Kohler.
Nature: Mishandling of a patent application.
Venue: U.S. District Court for the Northern District of California, San Jose Division.
Law firm: Kecker & Van Nest LLP, San Francisco, California.
Role: I served as technical expert witness on behalf of MLB and Kohler (Defendant). Negligence in conjunction with a patent application; I wrote one or more expert reports.
- 2011** *Case:* Koninklijke Philips Electronics N.V. versus Seoul Semiconductor (SSC) Company LTD.
Nature: Patent infringement.
Venue: U.S. District Court for the Central District of California Southern Division
Law firm: Latham & Watkins LLP, Washington DC.
Role: I served as technical expert witness on behalf of SSC (Defendant). I wrote one or more expert reports.
- 2011** *Case:* Jeou-Nan Tseng versus Home Depot USA Inc. and Guangde LEDup Enterprise Inc.
Nature: Patent infringement.
Venue: U.S. District Court for the Western District of Washington at Seattle.
Law firm: DLA Piper, Philadelphia, Pennsylvania.
Role: I served as technical expert witness on behalf of Home Depot (Defendant). I wrote one or more expert reports.
- 2011** *Case:* Lightpanels Ltd. Company versus Fuzhou F&V Photographic Company.
Nature: Patent infringement.
Venue: U.S. International Trade Commission (ITC), Washington DC.
Law firm: Locke Lord LLP, New York, New York.
Role: I served as technical expert witness on behalf of Fuzhou F&V and Nanguang Photographic (Defendant). I wrote one or more expert reports; I was deposed.
- 2012** *Case:* Osram Company versus LG Company.
Nature: Patent infringement.
Venue: U.S. International Trade Commission (ITC), Washington DC.
Law firm: Finnegan, Henderson, Farabow, Garrett & Dunner, LLP, Washington DC.
Role: I served as technical expert witness on behalf of LG (Defendant). I wrote one or more expert reports; I was deposed; I testified at the ITC Hearing.
- 2012** *Case:* Osram Company versus LG Company and Samsung Company.
Nature: Patent infringement.
Venue: U.S. International Trade Commission (ITC), Washington DC.
Law firm: Covington & Burling LLP, Washington DC.
Role: I served as technical expert witness on behalf of LG and Samsung (Defendant). I wrote one or more expert reports; I was deposed; I testified at the ITC Hearing.
- 2013** *Case:* Chao Tai Electron Co. LTD. versus LEDup Enterprise Inc. and others.
Nature: Patent infringement.
Venue: U.S. District Court for the Central District of California.
Law firm: Hunton & Williams LLP, Washington DC.
Role: I served as technical expert witness on behalf of LEDup Enterprise Inc. and others (Defendants). I wrote one or more expert reports.
- 2013** *Case:* Nichia Corporation versus Everlight Company and Emcore Company.
Nature: Inter Partes Review (IPR).
Venue: USPTO Patent Trial and Appeal Board.

- Law firm:** Foley & Lardner LLP, Washington DC.
Role: I served as technical expert witness on behalf of Nichia Corporation (Petitioner). I wrote one or more expert reports; I was deposed.
- 2014** **Case:** Everlight Electronics Co. LTD. versus Nichia Corporation.
Nature: Patent infringement.
Venue: U.S. District Court for the Eastern District of Michigan, Southern Division.
Law firm: Foley & Lardner LLP, Washington DC.
Role: I served as technical expert witness on behalf of Nichia Corporation (Defendant). I wrote one or more expert reports; I was deposed; I testified at Phase 1 of trial (jury trial) and I testified at Phase 2 of trial (bench trial).
- 2014** **Case:** LEDup Company versus Nicolas Holiday Company.
Nature: Patent infringement.
Venue: U.S. District Court for the Central District of California.
Law firm: Pendleton, Wilson, Hennessey, and Crow PC, Denver, Colorado.
Role: I served as technical expert witness on behalf of LEDup (Plaintiff). I wrote one or more expert reports.
- 2014** **Case:** Nichia Corporation versus Everlight Electronics Co. LTD.
Nature: Patent infringement.
Venue: U.S. District Court for the Eastern District of Texas, Marshall Division.
Case number: 02:13-cv-702-JRG (E.D. Texas).
Law firm: Rothwell, Figg, Ernst & Manbeck PC, Washington DC.
Role: I served as technical expert witness on behalf of Nichia (Plaintiff). I wrote one or more expert reports; I was deposed; I testified at trial (bench trial).
- 2015** **Case:** Cree Company versus Unity Opto, Unity Microelectronics, and Feit Electric Company
Nature: Patent infringement.
Venue: U.S. International Trade Commission (ITC), Washington DC.
Law firm: Alston & Bird LLP, Silicon Valley, East Palo Alto, California.
Role: I served as expert witness on behalf of Unity Opto Technology *et al.* (Defendants). I wrote one or more expert reports; I was deposed; I testified at trial (ITC Hearing).
- 2015** **Case:** Honeywell International Inc. versus Cree Inc.
Nature: Inter Partes Review (IPR).
Venue: USPTO Patent Trial and Appeal Board.
Law firm: Arnold & Porter LLP, San Francisco, California.
Role: I served as expert witness on behalf of Honeywell International Inc. (Plaintiff). I wrote one or more expert reports.
- 2015** **Case:** Honeywell International Inc. versus Cree Inc.
Nature: Patent infringement.
Venue: U.S. District Court for the District of New Jersey.
Law firm: Arnold & Porter LLP, San Francisco, California.
Role: I served as expert witness on behalf of Honeywell International Inc. (Plaintiff).
- 2015** **Case:** Cree Inc. versus Kingbright Electronic Co. LTD and SunLED Corporation.
Nature: Patent infringement.
Venue: U.S. District Court for the Western District of Wisconsin.
Law firm: Hansen Reynolds Dickinson Crueger LLC, Milwaukee, Wisconsin.
Role: I served as technical expert witness on behalf of Kingbright and SunLED (Defendants). I wrote one or more expert reports; I was deposed.

- 2016** *Case:* Acuity Brands Lighting Inc. versus Lynk Labs Inc.
Nature: Inter Partes Review (IPR).
Venue: USPTO Patent Trial and Appeal Board.
Law firm: Haynes Boone LLP, Chicago, Illinois.
Role: I served as technical expert witness on behalf of Lynk Labs (Plaintiff). I wrote one or more expert reports.
- 2016** *Case:* Godo Kaisha IP Bridge 1 Company versus Broadcom Company and others.
Nature: Patent infringement.
Venue: U.S. District Court for the Eastern District of Texas, Marshall Division.
Law firm: Ropes and Gray LLP, New York City, New York.
Role: I served as technical expert witness on behalf of IP Bridge 1 (Plaintiff). I wrote one or more expert reports; I was deposed.
- 2016** *Case:* TSMC Company versus Godo Kaisha IP Bridge 1 Company.
Nature: Inter Partes Review (IPR).
Venue: USPTO Patent Trial and Appeal Board.
Law firm: Greenblum & Bernstein, P.L.C., Reston, Virginia.
Role: I served as technical expert witness on behalf of IP Bridge (Patent Owner). I wrote one or more expert reports; I was deposed.
- 2017** *Case:* Harvard University versus Micron Technology Company.
Nature: Patent infringement.
Venue: U.S. District Court for MA, Boston; U.S. District Court for Delaware, Wilmington.
Law firm: Weil Gotshal & Manges LLP, Redwood Shores, California.
Role: I served as technical expert witness on behalf of Micron Technology Company (Defendant). I wrote one or more expert reports; I was deposed.
- 2017** *Case:* Seoul Viosys Company versus P3 Company.
Nature: Patent infringement.
Venue: U.S. District Court, Southern District of New York, New York City.
Law firm: Holland & Knight LLP, New York City, New York.
Role: I served as technical expert witness on behalf of Seoul Viosys (Plaintiff). I wrote one or more expert reports.
- 2017** *Case:* Nitride Semiconductor Company versus Rayvio Company.
Nature: Patent infringement.
Venue: US District Court for the Northern District of California.
Law firm: Dentons LLP, Palo Alto, California.
Role: I served as technical expert witness on behalf of Rayvio (Defendant).
- 2018** *Case:* CRX Tech LLC versus Samsung Electronics Co. LTD.
Nature: Patent infringement.
Venue: U.S. District Court for the Eastern District of Texas, Marshall Division.
Law firm: Arnold & Porter LLP, Los Angeles, California.
Role: I served as technical expert witness on behalf of Samsung (Defendant).
- 2018** *Case:* Macom Technology Solutions Holdings Inc. versus Infineon Technologies AG.
Nature: Patent infringement.
Venue: U.S. District Court Central District of California Western Division, Los Angeles.
Law firm: Perkins Coie LLP, Denver, Colorado.

Role: I served as technical expert witness on behalf of Macom (Plaintiff). I wrote one or more expert reports; I was deposed.

- 2018** **Case:** Vizio Inc. versus Nichia Corporation.
Nature: Inter Partes Review (IPR).
Venue: USPTO Patent Trial and Appeal Board.
Case number: Case No. IPR-2017-01608 and IPR-2017-01623 (PTAB).
Law firm: Rothwell, Figg, Ernst & Manbeck, P.C., Washington DC.
Role: I served as technical expert witness on behalf of Nichia Corporation (Patent Owner). I wrote one or more expert declarations.
- 2018** **Case:** Lowe's Companies Inc. versus Nichia Corporation.
Nature: Inter Partes Review (IPR).
Venue: USPTO Patent Trial and Appeal Board.
Case number: Case No. IPR2017-02014 (PTAB).
Law firm: Rothwell, Figg, Ernst & Manbeck, P.C., Washington DC.
Role: I served as technical expert witness on behalf of Nichia Corporation (Patent Owner). I wrote one or more expert declarations.
- 2018** **Case:** Ultravision Technologies LLC versus Prismaflex USA Inc.
Nature: Patent infringement.
Venue: US International Trade Commission (ITC), Washington DC.
Case number: Investigation No. 337-TA-1114 (ITC)
Law firm: Womble Bond Dickinson LLP, Winston-Salem, NC
Role: I served as technical expert witness on behalf of Prismaflex USA (Defendant). I wrote one or more expert reports. I was deposed.
- 2019** **Case:** Carl Zeiss AG versus Nikon USA Inc.
Nature: Patent infringement.
Venue: US International Trade Commission (ITC), Washington DC.
Case number: Investigation No. 337-TA-1129 (US ITC)
Law firm: Morrison & Foerster LLP, Los Angeles CA.
Role: I served as technical expert witness on behalf of Nikon USA (Defendant). I wrote one or more expert reports. I was deposed.
- 2019** **Case:** ASM IP Holding B.V. versus Hitachi Kokusai Electric Inc.
Nature: Arbitration related to IP licensing dispute.
Venue: ICDR (International Center for Dispute Resolution), Palo Alto CA.
Case number: Case No. ICDR 01-17-0005-1963 (Palo Alto CA)
Law firm: Quinn Emanuel Urquhart & Sullivan LLP, San Francisco CA.
Role: I served as technical expert witness on behalf of ASM IP Holding B.V. (Complainant). I authored multiple witness statements. I testified at the Arbitration Hearing.
- 2019** **Case:** Power Integrations Inc. versus C. W. Park.
Nature: Breach of employment contract.
Venue: US District Court, Northern District of California, San Jose Division.
Case number: 5:16-cv-02366-BLF (Northern District of California)
Law firm: Miclean Gleason LLP, San Mateo CA.
Role: I served as technical expert witness on behalf of Power Integrations Inc. (Complainant). I performed analyses relating to switched-mode power supplies (SMPS) including flyback transformers. The matter ended in settlement.

- 2019** **Case:** Omni MedSci Inc. versus Apple Inc.
Nature: Patent infringement.
Venue: US District Court, Eastern District of Texas, Marshall Division.
Case number: Civil Action No. 2:18-cv-134-RWS (E.D. Texas)
Law firm: Sidley Austin LLP, Washington DC.
Role: I served as technical expert witness on behalf of Apple Inc. (Defendant). I performed a non-infringement analysis relating to the heart rate monitor of the Apple Watch, authored an expert report, and testified at a deposition.
- 2019** **Case:** Fluxwerx Illumination Inc., versus OKT Lighting USA LLC
Nature: Design patent infringement.
Venue: US District Court, Southern District of Texas, Houston Division.
Case number: Civil Action No. 4:19-CV-01113 (S.D. Texas)
Law firm: Burns & Levinson LLP, Boston MA.
Role: I served as technical expert witness on behalf of Fluxwerx Illumination, Inc. (Plaintiff). I performed an infringement analysis.
- 2020** **Case:** Lighting Science Group Corporation versus Nichia Corporation and others
Nature: Patent infringement.
Venue: US ITC, Office for Unfair Import Investigations, Washington DC
Case number: Investigation No. 337-TA-1168
Law firm: Shearman & Sterling LLP, New York, NY.
Role: I served as technical expert witness on behalf of Nichia Corporation. I performed a non-infringement analysis, authored an expert report, was deposed, and testified at the ITC hearing as key technical witness on behalf of Nichia and Respondents (6 hours live testimony).
- 2020** **Case:** Regents of the University of California versus Amazon, Walmart, Ikea, Target, and others
Nature: Patent infringement.
Venue: US ITC, Office for Unfair Import Investigations, Washington DC
Case number: Investigation No. 337-TA-1172
Law firm: Nixon Peabody LLP, Los Angeles CA.
Role: I served as technical expert witness on behalf of the Regents of the University of California. I performed an infringement analysis, authored an expert report, and was deposed.
- 2020** **Case:** Samsung Electronics Company versus Acorn Technologies Company.
Nature: USPTO Inter Partes Review.
Venue: USPTO, Patent Trial and Appeal Board, Alexandria VA.
Case numbers: IPR-2020-01183 ('261), IPR-2020-01182 ('423), IPR-2020-01204 ('336), IPR-2020-01264 ('336), IPR-2020-01205 ('167), IPR-2020-01241 ('167), IPR-2020-01206 ('691), IPR-2020-01279 ('691), IPR-2020-01207 ('395), and IPR-2020-01282 ('395)
Law firm: Desmarais LLP, New York NY.
Role: I served as technical expert witness on behalf of Samsung Electronics Company. I authored several expert declarations and was deposed multiple times.
- 2020** **Case:** Satco Company versus The Regents of the University of California.
Nature: USPTO Inter Partes Review.
Venue: USPTO, Patent Trial and Appeal Board, Alexandria VA.
Case numbers: IPR-2020-00579, IPR-2020-00695, IPR-2020-00780, and IPR-2020-00813.
Law firm: Nixon Peabody LLP, Los Angeles CA.
Role: I served as technical expert witness on behalf of The Regents of the University of California. I authored several expert declarations and was deposed.

- 2020** *Case:* Godo Kaisha IP Bridge 1 Company versus Micron Technology Company.
Nature: Patent infringement.
Venue: US District Court for the Western District of Texas, Waco Division.
Case number: C.A. No. 6:20-cv-178-ADA.
Law firm: Orrick Herrington & Sutcliffe LLP, Menlo Park CA.
Role: I served as technical expert witness on behalf of Micron Technology Company. I authored multiple expert reports and was deposed.
- 2020** *Case:* Nichia Company versus Healtel Company and Lighting Science Group Company.
Nature: Patent infringement.
Venue: US District Court for the Middle District of Florida, Orlando Division.
Case numbers: 6:19-cv-1332-RBD-EJK and 6:19-cv-1333-RBD-EJK.
Law firm: Rothwell, Figg, Ernst & Manbeck, PC, Washington DC.
Role: I served as technical expert witness on behalf of Nichia Company. I authored one or more expert reports.
- 2020** *Case:* Semiconductor Energy Laboratory (SEL) Co., Ltd. versus BOE Technology Group Co., Ltd.
Nature: Patent infringement.
Venue: US District Court for the Northern District of California.
Case number: 3:20-cv-04297-EMC, N.D. Cal.
Law firm: Fish and Richardson, P.C., Redwood City CA.
Role: I served as technical expert witness on behalf of SEL.
- 2021** *Case:* The University of California versus General Electric, Ikea, Home Depot and others
Nature: Patent infringement.
Venue: US ITC, Office for Unfair Import Investigations, Washington DC
Case number: Investigation No. 337-TA-1220
Law firm: Nixon Peabody LLP, Los Angeles CA.
Role: I served as technical expert witness on behalf of the University of California. I performed multiple analyses, authored several expert reports, was deposed multiple times, and testified at trial.
- 2021** *Case:* Tianma Microelectronics Co., Ltd. versus Japan Display Inc. (JDI)
Nature: USPTO Inter Partes Review.
Venue: USPTO, Patent Trial and Appeal Board, Alexandria VA
Case numbers: IPR-2021-01029, IPR-2021-01057 and IPR-2021-01058
Law firm: Finnegan, Henderson, Farabow, Garrett & Dunner, LLP, Washington DC.
Role: I served as technical expert witness on behalf of Tianma. I performed multiple analyses and authored several declarations.
- 2021** *Case:* Japan Display Inc. (JDI) versus Tianma Microelectronics Co., Ltd.
Nature: Patent infringement.
Venue: US District Court for the Eastern District of Texas, Marshall Division.
Case numbers: Civil Action No. 2:20-cv-00283-JRG; 2:20-cv-00284-JRG; and 2:20-cv-00285-JRG
Law firm: Finnegan, Henderson, Farabow, Garrett & Dunner, LLP, Washington DC.
Role: I served as technical expert witness on behalf of Tianma. I performed multiple analyses, authored several expert reports, and was deposed multiple times.
- 2022** *Case:* Satco Products Inc. versus The Regents of the University of California.
Nature: USPTO Inter Partes Review.
Venue: USPTO, Patent Trial and Appeal Board, Alexandria VA.
Case number: IPR-2021-00662.
Law firm: Nixon Peabody LLP, Los Angeles CA.

Role: I served as technical expert witness on behalf of The Regents of the University of California, authored one expert declaration, and was deposed.

2022 Case: Samsung Electronics Co. Ltd. versus Bishop Display Tech LLC.

Nature: USPTO Inter Partes Review.

Venue: USPTO, Patent Trial and Appeal Board, Alexandria VA.

Case numbers: IPR-2022-00500 and IPR-2022-00502.

Law firm: Baker Botts LLP, New York City NY.

Role: I served as technical expert witness on behalf of Samsung Electronics and have authored two expert declarations.

2022 Case: Semiconductor Energy Laboratory (SEL) Co. Ltd. versus TCL China Star Optoelectronics Technology Co., Ltd.

Nature: Patent infringement.

Venue: US District Court for the Central District of California, Southern Division.

Case number: 8:21-cv-00554-JAK-ADS.

Law firm: Fish and Richardson, P.C., Redwood City CA.

Role: I served as technical expert witness on behalf of SEL, authored two expert reports, and was deposed.

2022 Case: Nvidia Corporation versus Ocean Semiconductors LLC.

Nature: USPTO Inter Partes Review.

Venue: USPTO, Patent Trial and Appeal Board, Alexandria VA.

Case number: IPR2022-01288.

Law firm: Sheppard Mullin LLP, Menlo Park CA.

Role: I served as technical expert witness on behalf of Nvidia and authored one expert declaration.

2022 Case: Nicor, Inc. versus SourceBlue LLC and InfiniLux Corporation.

Nature: Patent infringement.

Venue: US District Court for the Central District of California.

Case number: 2:21-cv-05876-AB(PDx) (C.D. Cal.).

Law firm: Loza & Loza IP LLP, Upland CA.

Role: I served as technical expert witness on behalf of Nicor, Inc., authored three expert reports, and was deposed.

2023 Case: Dr. Shimon Maimon versus Lockheed Martin Corporation.

Nature: Dispute relating to a License Agreement.

Venue: JAMS ADR (Alternative Dispute Resolution).

Case number: JAMS Ref. No. 1460005932.

Law firm: Finnegan, Henderson, Farabow, Garrett & Dunner, LLP, Washington DC.

Role: I served as technical expert witness on behalf of Lockheed Martin Corporation, authored three expert reports, was deposed, and testified at the Hearing.

2023 Case: Samsung Electronics Co. Ltd. versus Daedalus Prime LLC.

Nature: USPTO Inter Partes Review.

Venue: USPTO, Patent Trial and Appeal Board, Alexandria VA.

Case numbers: IPR2023-00536 and IPR2023-00653.

Law firm: Fish & Richardson PC, Minneapolis MN.

Role: I served as technical expert witness on behalf of Samsung Electronics and authored two expert declarations.

- 2023** *Case:* Seoul Semiconductor Co. Ltd., et al. versus GE Healthcare Inc.
Nature: Patent infringement.
Venue: United States District Court for the District of Delaware.
Case number: Civil Action No. 1:22-cv-01455.
Law firm: Shearman & Sterling LLP, New York, NY.
Role: I served as technical expert witness on behalf of GE Healthcare.
- 2023** *Case:* Efficient Power Conversion Corp. versus Innoscience (Zhuhai) Technology Company.
Nature: Patent infringement.
Venue: US International Trade Commission (ITC), Washington DC.
Case number: Investigation No. 337-TA-1366.
Law firm: Blank Rome LLP, Washington DC
Role: I served as technical expert witness on behalf of EPC, authored multiple expert reports, was deposed, and testified at the ITC Hearing.
- 2023** *Case:* Innoscience (Zhuhai) Technology Company versus Efficient Power Conversion Corp.
Nature: USPTO Inter Partes Review.
Venue: USPTO, Patent Trial and Appeal Board, Alexandria VA.
Case numbers: IPR2023-01381, IPR2023-01382, IPR2023-01383, and IPR2023-01384.
Law firm: Blank Rome LLP, Washington DC.
Role: I served as technical expert witness on behalf of Efficient Power Conversion Corp. and authored multiple expert declarations.
- 2023** *Case:* Xu Peicheng (Hong Kong) Optoelectronic Technol. Co. versus SemiSilicon Technol. Corp.
Nature: USPTO Inter Partes Review.
Venue: USPTO, Patent Trial and Appeal Board, Alexandria VA.
Case numbers: IPR2024-00156 and IPR2024-00157 (US Patent 8,124,988 and US 8,884,546)
Law firm: Rimon Law PC, McLean VA.
Role: I served as technical expert witness on behalf of Xu Peicheng and authored two expert declarations.
- 2024** *Case:* Seasonal Specialties, LLC versus LEDUP Manufacturing Group LTD.
Nature: Patent infringement.
Venue: US District Court, Central District of California, Western Division.
Case number: 2:23-cv-06318-SB-AS.
Law firm: Fairfield & Woods PC, Denver CO.
Role: I served as technical expert witness on behalf of LEDUP Manufacturing Group and composed multiple Invalidity Claim Charts, and multiple Expert Declarations.
- 2024** *Case:* Wuxi Autowell Technology Co. Ltd. versus Teamtechnik Maschinen und Anlagen GmbH.
Nature: USPTO Inter Partes Review.
Venue: USPTO, Patent Trial and Appeal Board, Alexandria VA.
Case numbers: US patent numbers 8,247,681 and 8,253,009.
Law firm: Novick, Kim & Lee, PLLC, (NKL Law), Fairfax VA.
Role: I served as technical expert witness on behalf of Wuxi Autowell Technology and composed one expert declaration.
- 2024** *Case:* Greenthread LLC versus Omnivision Technologies, Inc., and Texas Instruments, Inc.
Nature: Patent infringement.
Venue: US District Court, Eastern District of Texas, Marshall Division.
Case numbers: 2:23-cv-00212-JRG and 2:23-cv-00157-JRG.
Law firms: Benesch Friedlander Coplan & Aronoff LLP and Caldwell Cassidy & Curry PC.

- Role:** I served as technical expert witness on behalf of Omnivision Technologies and Texas Instruments, composed one expert declaration, and was deposed.
- 2024** **Case:** Lian Li Industrial Co. Ltd. and CHEN, Chien-Hao versus Thermaltake Technology Co. Ltd.
Nature: Patent infringement.
Venue: US District Court, Central District of California.
Case number: 2:23-cv-07470.
Law firm: The Gikkas Law Firm, PC, Palo Alto CA
Role: I served as technical expert witness on behalf of Thermaltake Technology, composed one expert declaration, and was deposed.
- 2024** **Case:** Pictiva Displays International Ltd. versus Samsung Electronics Co. Ltd.
Nature: Patent infringement.
Venue: US District Court, Eastern District of Texas, Marshall Division.
Case number: 2:23-cv-00495-JRG.
Law firm: Quinn Eamanuel Urquhart & Sullivan LLP, Seattle WA.
Role: I served as technical expert witness on behalf of Samsung Electronics Co., composed one expert declaration, and was deposed.
- 2024** **Case:** Feit Electric Company versus Savant Technologies and additional parties
Nature: Patent infringement.
Venue: US District Court, Northern District of Ohio and additional venues.
Case number: 1:24-cv-473.
Law firm: Benesch, Friedlander, Coplan & Aronoff LLP, Chicago ILL.
Role: I served as technical expert witness on behalf of Feit Electric Company, composed one or more expert declarations, and was deposed.
- 2024** **Case:** Savant Technologies LLC and LEDvance LLC versus Feit Electric Company.
Nature: USPTO Inter Partes Review.
Venue: USPTO, Patent Trial and Appeal Board, Alexandria VA.
Case number: US patent number 8,604,678. IPR2024-01357.
Law firm: Novick, Kim & Lee, PLLC, (NKL Law), Fairfax VA.
Role: I served as technical expert witness on behalf of Feit Electric Company and composed one expert declaration.
- 2024** **Case:** 138 East LCD Advancements Ltd. versus BOE Technology Group Co., Ltd.
Nature: Patent infringement.
Venue: US District Court, Eastern District of Texas, Marshall Division.
Case number: 2:23-cv-515-JRG-RSP.
Law firm: Robins Kaplan LLP Law Firm, Minneapolis MN.
Role: I served as technical expert witness on behalf of 138 East LCD Advancements Ltd. and composed multiple expert declarations, and was deposed.
- 2024** **Case:** BOE Technology Group Co., Ltd. versus 138 East LCD Advancements Ltd.
Nature: USPTO Inter Partes Review.
Venue: USPTO, Patent Trial and Appeal Board, Alexandria VA.
Case numbers: IPR2024-00973, IPR2024-00977, and IPR2024-00977.
Law firm: Robins Kaplan LLP, Minneapolis MN.
Role: I served as technical expert witness on behalf of 138 East LCD Advancements Ltd., composed multiple expert declarations, and was deposed.
- 2025** **Case:** YMTC (Yangtze Memory Technologies Company, Ltd.) versus Micron Technology Inc.
Nature: Patent infringement.
Venue: US District Court, Northern District of California

Case number: 3:23-cv-05792-RFL.

Law firm: Orrick, Herrington & Sutcliffe LLP.

Role: I served as technical expert witness on behalf of Micron Technology Inc. and composed one expert declaration.

2025 Case: Hanwha Solutions Corporation, Petitioner versus Maxeon Solar PTE. LTD., Patent Owner

Nature: USPTO Inter Partes Review.

Venue: USPTO, Patent Trial and Appeal Board, Alexandria VA.

Case number: IPR2024-01198.

Law firm: PV Law LLP, Washington DC.

Role: I served as technical expert witness on behalf of Maxeon Solar PTE. LTD, composed one expert declaration, and was deposed.

United States Patents

1. A. Fischer, Y. Horikoshi, K. Ploog, and E. F. Schubert "Semiconductor devices with at least one monoatomic layer of doping atoms" European Patent No. 0183 146 A2; US Patent No. 4,882,609; issued on November 15 (1985)
2. J. E. Cunningham, E. F. Schubert, and W. T. Tsang "Delta doped ohmic metal to semiconductor contacts" US Patent No. 4,772,934; issued on September 20 (1988)
3. J. E. Cunningham, E. F. Schubert, and W. T. Tsang "Field-effect transistor having a delta-doped ohmic contact" US Patent No. 4,780,748; issued on October 25 (1988)
4. J. E. Cunningham, E. F. Schubert, and W. T. Tsang "Method for fabricating a field-effect transistor with a self-aligned gate" US Patent No. 4,784,967; issued on November 15 (1988)
5. E. Fred Schubert "Optical communications modulator device" US Patent No. 4,929,064; filed on July 21 (1988) issued on May 29 (1990)
6. J. E. Cunningham, A. M. Glass, and E. F. Schubert "Devices having asymmetric delta-doping" US Patent No. 4,974,044; issued on November 27 (1990)
7. J. E. Cunningham, A. M. Glass, and E. F. Schubert "Devices having asymmetric delta-doping" US Patent No. 5,031,012; issued on July 9 (1991)
8. J. E. Cunningham, T. D. Harris, E. F. Schubert, and J. P. van der Ziel "Optical system including wavelength tunable semiconductor laser" US Patent No. 4,980,892; issued on December 25 (1990)
9. R. F. Kopf, J. M. Kuo, H. S. Luftman, and E. F. Schubert "Doping procedures for semiconductor devices" US Patent No. 5,024,967; issued on June 18 (1991)
10. D. G. Deppe, R. D. Dupuis, and E. F. Schubert "Vertical cavity semiconductor lasers" US Patent No. 5,018,157; issued on May 21 (1991)
11. D. G. Deppe, L. C. Feldman, R. F. Kopf, E. F. Schubert, L.-W. Tu, and G. J. Zyzdik "Vertical cavity surface emitting lasers with electrically conducting mirrors" US Patent No. 5,068,868; issued on November 26 (1991)
12. D. G. Deppe, E. F. Schubert, L.-W. Tu, and G. D. Zyzdik "Optical devices with electron-beam evaporated multilayer mirror" US Patent No. 5,206,871; issued on April 27 (1993)
13. R. F. Kopf, E. F. Schubert, H. O'Brian, L.-W. Tu, Y. H. Wang, and G. J. Zyzdik "Vertical cavity surface emitting lasers with transparent electrodes" US Patent No. 5,115,441; issued on May 19 (1992)
14. E. F. Schubert, L.-W. Tu, and G. J. Zyzdik "Elimination of heterojunction band discontinuities" US Patent No. 5,170,407; issued on December 8 (1992)
15. S. W. Downey, A. B. Emerson, R. F. Kopf, and E. F. Schubert "Devices having repetitive layers" US Patent No. 5,226,055; issued on July 6 (1993)
16. A. Y. Cho, E. F. Schubert, L.-W. Tu, and G. J. Zyzdik "Resonant cavity light emitting diode" US Patent No. 5,226,053; issued on July 6 (1993)
17. L. C. Feldman, N. E. J. Hunt, D. C. Jacobson, J. M. Poate, E. F. Schubert, A. M. Vredenberg, Y. H. Wong, and G. J. Zyzdik "Erbium-doped optical devices" US Patent No. 5,249,195; issued on September 28 (1993)

18. R. F. Kopf and E. F. Schubert "PN junction devices with group IV element-doped group III-V compound semiconductors" US Patent No. 5,268,582; issued on December 7 (1993)
19. N. E. J. Hunt and E. F. Schubert "Single mirror light-emitting diodes with enhanced intensity" US Patent No. 5,362,977; issued on November 8 (1994)
20. N. E. J. Hunt, E. F. Schubert, and G. J. Zydzik "Photodetector with a resonant cavity" US Patent No. 5,315,128; issued on May 24 (1994)
21. A. M. Glass, N. E. J. Hunt, J. M. Poate, E. F. Schubert, and G. J. Zydzik "Absorption resonant rare-earth-doped microcavities" US Patent No. 5,363,398; issued on November 8 (1994)
22. N. E. J. Hunt, M. Passlack, E. F. Schubert, and G. J. Zydzik "Electron beam deposition of gallium oxide thin films using a single high purity crystal source" US Patent No. 5,451,548; issued on September 19 (1995)
23. N. K. Dutta, R. J. Fischer, N. E. J. Hunt, M. Passlack, E. F. Schubert, and G. J. Zydzik "Gallium oxide coatings for optoelectronic devices using electron beam evaporation of a high purity single crystal $\text{Gd}_3\text{Ga}_5\text{O}_{12}$ source" US Patent No. 5,550,089; issued on August 27 (1996)
24. U. K. Chakrabarti, J. de Jong, E. F. Schubert, J. Wynn, and G. J. Zydzik "Mechanical fixture and procedure for in-vacuum coating of semiconductor laser facets" US Patent No. 5,719,077; issued on February 17 (1998)
25. E. F. Schubert "Enhanced p-type doping of wide-gap semiconductors" US Patent No. 5,932,899; issued on August 3 (1999)
26. J. D. Joannopoulos, S. Fan, P. R. Villeneuve, and E. F. Schubert "Light emitting device utilizing a periodic dielectric structure" US Patent No. 5,955,749; issued on September 21 (1999)
27. E. F. Schubert and D. A. Stocker "Crystallographic wet chemical etching on GaN" US Patent No. 6,294,475; issued on September 25 (2001)
28. E. F. Schubert "Light-emitting diode with omni-directional reflector" US Patent No. 6,784,462; issued on August 31 (2004)
29. Jaehee Cho, Hong Luo, Jong Kyu Kim, Yong Jo Park, Cheolsoo Sone, and E. Fred Schubert "Light emitting device having protection element and method of manufacturing the light emitting device" US Patent No. 7,411,221 B2; issued on August 12 (2008)
30. Jaehee Cho, Frank Wilhelm Mont, Cheolsoo Sone, Jong-kyu Kim, June-o Song, E. Fred Schubert "Optical thin film, semiconductor light emitting device having the same and methods of fabricating the same" US Patent No. 7,483,212; issued on January 27 (2009)
31. Jaehee Cho, Martin F. Schubert, E. Fred Schubert, Jong Kyu Kim, Cheolsoo Sone "Light emitting diodes and display apparatuses using the same" US Patent No. 7,560,746; issued on July 14 (2009)
32. Martin F. Schubert, Sameer Chhajed, Jong Kyu Kim, E. Fred Schubert, and Jaehee Cho "Reflector shapes for light-emitting diode-polarized light sources" US Patent No. 7,766,495; filed on June 24 (2008); issued on August 3 (2010)
33. Martin F. Schubert, Ahmed Noemaun, Sameer Chhajed, Jong Kyu Kim, E. F. Schubert, Cheolsoo Sone "Encapsulant shapes for light emitting devices lacking rotational symmetry designed to enhance extraction of light with a particular linear polarization" US Patent No. 7,819,557; filed on June 24 (2008); issued on October 6 (2010)

34. Jaehee Cho, Jong-Kyu Kim, Cheolsoo Sone, and E. F. Schubert “LED device having diffuse reflective surface” US Patent No. 7,816,855; filed on December 28 (2005); issued on October 19 (2010)
35. Jaehee Cho, E. Fred Schubert, and Xing Yan “Liquid crystal display with refractive index matched electrodes” US Patent No. 8,164,727; filed on April 28, 2010; issued on April 24 (2012)
36. Mary H. Crawford, Daniel Koleske, Jaehee Cho, Di Zhu, Ahmed Noemaun, Martin F. Schubert, and E. Fred Schubert “High efficiency III-Nitride light-emitting diodes” US Patent No. 8,451,877; filed on March 17, 2011; issued on May 28 (2013)
37. Min-ho Kim, Martin F. Schubert, Jong Kyu Kim, E. Fred Schubert, Yongjo Park, Cheolsoo Sone, and Sukho Yoon “Nitride semiconductor light-emitting device” US Patent No. 8,502,266; filed on September 8 (2010); issued on August 6 (2013)
38. David J. Poxson, Frank W. Mont, E. Fred Schubert, and Richard W. Siegel “Tunable nanoporous film on polymer substrates, and method for their manufacture” US Patent No. 9,732,427; filed on April 23 (2013); issued on August 15 (2017)
39. Sameer Chhajed, Jong Kyu Kim, Shawn-Yu Lin, Mei-Ling Kuo, Frank W Mont, David J Poxson, E Fred Schubert, Martin F Schubert “Ultra-low reflectance broadband omni-directional anti-reflection coating” US Patent No. 11,088,291; filed on July 22 (2016); issued on August 10 (2021)

Patent Licensing: Several patents listed above have been licensed to companies, including the Luminus Devices Company, Samsung Company, Epistar Company, Cree Company, Osram Company, and Lumileds Company.

Journal Publications

1982

1. H. Künzel, H. Jung, E. F. Schubert, and K. Ploog "Influence of growth conditions and of alloy composition on electrical and optical properties of MBE AlGaAs" *Journal Physique Colloque C5*, **C5/175**, 42 (1982)

1984

2. E. F. Schubert, K. Ploog, H. Dämbkes, and K. Heime "Selectively doped n-AlGaAs/ GaAs heterostructures with high-mobility two-dimensional electron gas for field-effect transistors. Part I: Effect of parallel conductance" *Applied Physics* **A33**, 63 (1984)
3. E. F. Schubert, K. Ploog, H. Dämbkes., and K. Heime "Selectively doped n-AlGaAs/ GaAs heterostructures with high-mobility two-dimensional electron gas for field-effect transistors. Part II: Hot electron effects" *Applied Physics* **A33**, 183 (1984)
4. E. F. Schubert and K. Ploog "Transient photoconductivity in selectively doped n-type AlGaAs/GaAs heterostructures" *Physical Review* **B29**, 4562 (1984)
5. E. F. Schubert, E. O. Göbel, Y. Horikoshi, K. Ploog, and H. J. Queisser "Alloy broadening in photoluminescence spectra of AlGaAs" *Physical Review* **B30**, 813 (1984)
6. E. F. Schubert and K. Ploog "Shallow and deep donors in direct-gap n-AlGaAs:Si grown by molecular-beam epitaxy" *Physical Review* **B30**, 7021 (1984)

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7. E. F. Schubert, J. Knecht, and K. Ploog "Transient and persistent photoconductivity in n-AlGaAs and selectively doped n-AlGaAs/GaAs heterostructures" *Journal of Physics C: Solid-State Physics* **18**, L215 (1985)
8. E. F. Schubert, A. Fischer, and K. Ploog "GaAs sawtooth superlattice light-emitting diode operating monochromatically at $\lambda > 0.9 \mu\text{m}$ " *Electronics Letters* **21**, 411 (1985)
9. E. F. Schubert, A. Fischer, Y. Horikoshi, and K. Ploog "GaAs sawtooth superlattice laser emitting at wavelengths $\lambda > 0.9 \mu\text{m}$ " *Applied Physics Letters* **47**, 219 (1985)
10. E. F. Schubert, A. Fischer, and K. Ploog "Electron-impurity tunneling in selectively doped n-type AlGaAs/GaAs heterostructures" *Physical Review* **B31**, 7937 (1985)
11. E. F. Schubert, Y. Horikoshi, and K. Ploog "Radiative electron-hole recombination in a new sawtooth semiconductor superlattice grown by molecular-beam epitaxy" *Physical Review* **B32**, 1085 (1985)
12. E. F. Schubert and K. Ploog "The delta-doped field-effect transistor" *Japanese Journal Applied Physics Letters* **24**, L608 (1985)
13. K. Ploog, A. Fischer, E. F. Schubert "Preparation and properties of a new GaAs sawtooth doping superlattice" *Proceedings of the Second International Conference (Yamada Conference) on Modulated Semiconductor Structures*; September 9-13 (1985), Kyoto, Japan
14. E. F. Schubert and K. Ploog "Electron subband structure in selectively doped n-AlGaAs/ GaAs heterostructures" *IEEE Transactions on Electron Devices*, **ED-32**, 1868 (1985)
15. E. F. Schubert and K. Ploog "Optical properties of a new sawtooth superlattice grown by molecular beam epitaxy" *Journal de Physique (Paris)*, **46**, 147 (1985)

1986

16. E. F. Schubert, A. Fischer, and K. Ploog "The delta-doped field-effect transistor" *IEEE Transactions on Electron Devices*, **ED-33**, 625 (1986)
17. E. F. Schubert and K. Ploog "Interpretation of capacitance-voltage profiles from delta-doped GaAs grown by molecular-beam epitaxy" *Japanese Journal of Applied Physics* **25**, 966 (1986)
18. E. F. Schubert and W. T. Tsang "Photoluminescence line shape of excitons in alloy semiconductors" *Physical Review B, Rapid Communications*, **B34**, 2991 (1986)
19. E. F. Schubert, J. E. Cunningham, W. T. Tsang, and T. H. Chiu "Delta-doped ohmic contacts to n-GaAs" *Applied Physics Letters* **49**, 292 (1986) and *Applied Physics Letters* **49**, 984 (1986)
20. K. Ploog, A. Fischer, and E. F. Schubert "Preparation and properties of a new GaAs sawtooth doping superlattice" *Surface Science* **174**, 120 (1986)
21. B. I. Miller, E. F. Schubert, U. Koren, A. Ourmazd, A. H. Dayem, and R. J. Capik "High quality narrow GaInAs/InP quantum wells grown by atmospheric organometallic vapor phase epitaxy" *Applied Physics Letters* **49**, 1384 (1986)
22. E. F. Schubert, Cunningham J. E., and Tsang W. T. "Self-aligned enhancement and depletion-mode GaAs field-effect transistors employing the delta-doping technique" *Applied Physics Letters* **49**, 1729 (1986)

23. W. T. Tsang, E. F. Schubert, A. H. Dayem, J. E. Cunningham, T. H. Chiu, J. A. Ditzenberger, J. Shah, and J. L. Zyskind "Very high quality GaInAs grown by chemical beam epitaxy" *Journal of Electronic Materials* **15**, 307 (1986)
24. W. T. Tsang and E. F. Schubert "Extremely high quality GaInAs/InP quantum wells grown by chemical beam epitaxy" *Applied Physics Letters* **49**, 220 (1986)
25. W. T. Tsang, A. H. Dayem, T. H. Chiu, J. E. Cunningham, E. F. Schubert, J. A. Ditzenberger, J. Shah, J. L. Zyskind, and N. Tabatabaie "Chemical beam epitaxial growth of extremely high quality GaInAs on InP" *Applied Physics Letters* **49**, 170 (1986)
26. E. F. Schubert, A. Fischer, and K. Ploog "Photoconductivity in selectively n- and p-doped AlGaAs/GaAs heterostructures" *Solid-State Electronics* **29**, 173 (1986)

1987

27. E. F. Schubert, J. E. Cunningham, and W. T. Tsang "'Type A' sawtooth doping superlattice: realization of the Esaki-Tsu type superlattice" *Physical Review B Rapid Communications* **B36**, 1348 (1987)
28. E. F. Schubert, J. E. Cunningham, and W. T. Tsang "Electron-mobility enhancement and electron-concentration enhancement in delta-doped n-GaAs at $T = 300$ K" *Solid-State Communications* **63**, 591 (1987)
29. W. T. Tsang, E. F. Schubert, T. H. Chiu, J. E. Cunningham, E. G. Burkhardt, J. A. Ditzenberger, and E. Agyekum "Growth of high-quality GaInAsP by chemical beam epitaxy" *Applied Physics Letters* **51**, 761 (1987)
30. J. E. Cunningham, W. T. Tsang, T. H. Chiu, E. F. Schubert, and J. A. Ditzenberger "MBE grown high purity GaAlAs" *J. Vac. Sci. Technol.* **A5**, 761 (1987)
31. W. T. Tsang, E. F. Schubert, T. H. Chiu, J. E. Cunningham, and J. A. Ditzenberger "Chemical beam epitaxial growth of very high quality GaInAs and GaInAs/InP quantum well heterostructures" *GaAs and Related Compounds* (1987) Ed. by W. T. Lindley.
32. J. E. Cunningham, W. T. Tsang, T. H. Chiu, and E. F. Schubert "Molecular beam epitaxial growth of high purity AlGaAs" *Applied Physics Letters* **50**, 769 (1987)
33. Y. Horikoshi, A. Fischer, E. F. Schubert, and K. Ploog "High-mobility two-dimensional electron gas from delta-doped asymmetric AlGaAs/GaAs/AlGaAs quantum wells" *Japanese Journal Applied Physics* **26**, 263 (1987)
34. T. H. Chiu, E. Agyekum, J. A. Ditzenberger, A. Robertson, E. F. Schubert, W. T. Tsang, and C. W. Tu "Growth and characterization of (001) GaAs epilayers by chemical beam epitaxy" *Journal of Electronic Materials* **16**, A21 (1987)
35. E. F. Schubert, J. E. Cunningham, and W. T. Tsang "Perpendicular electronic transport in doping superlattices" *Applied Physics Letters* **51**, 817 (1987)
36. E. F. Schubert, J. E. Cunningham, W. T. Tsang, and G. L. Timp "Selectively delta-doped AlGaAs/GaAs heterostructures with two-dimensional electron-gas concentrations $n_{2\text{DEG}} \geq 1.5 \times 10^{12} \text{ cm}^{-2}$ for field-effect transistors" *Applied Physics Letters* **51**, 1170 (1987)
37. T. H. Chiu, W. T. Tsang, E. F. Schubert, and E. Agyekum "Chemical beam epitaxial growth of high-purity GaAs using trimethylgallium and arsine" *Applied Physics Letters* **51**, 1109 (1987)

1988

38. B. Ullrich, E. F. Schubert, J. Stark, and J. E. Cunningham "Localization of impurities in delta-doped n-type GaAs" *Applied Physics* **A47**, 123 (1988)
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